

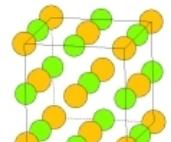
# Atomic-Scale Investigations of Dislocations and Interfaces in Telluride-Based Thermoelectric Materials

Douglas L. Medlin  
Sandia National Laboratories  
Livermore, CA 94551 USA  
*dlmedli@sandia.gov*

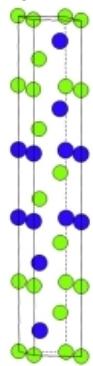
*Sandia National Laboratories is a multi-program laboratory managed and operated by Sandia Corporation, a wholly owned subsidiary of Lockheed Martin Corporation, for the U.S. Department of Energy's National Nuclear Security Administration under contract DE-AC04-94AL85000.*

# Our focus: Extended Defects in Tellurides

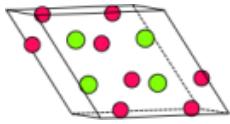
Rock-Salt  
(PbTe, AgSbTe<sub>2</sub>)



Tetradymite  
(Bi<sub>2</sub>Te<sub>3</sub>, Sb<sub>2</sub>Te<sub>3</sub>)



Monoclinic  
(Ag<sub>2</sub>Te)



Rich set of structures and phase relations

## Longstanding importance as thermoelectrics

-Bi<sub>2</sub>Te<sub>3</sub>-based alloys widely used for cooling and some low grade waste heat recovery applications

-p-type : (Bi<sub>0.2</sub>Sb<sub>0.8</sub>)<sub>2</sub>Te<sub>3</sub>

-n-type Bi<sub>2</sub>(Te<sub>0.9</sub>Se<sub>0.1</sub>)<sub>3</sub>

-PbTe and (GeTe)<sub>x</sub>(AgSbTe<sub>2</sub>)<sub>1-x</sub>:

-higher T application

-unattended operation.

## Broader interest in Tellurides and related Chalcogenides

-Topological insulators, catalysis, phase-change memory

-2d materials, intergrowth compounds

**Interface control:** strategy for tailoring thermal and electronic transport.

**Can we begin to make sense of interfaces and dislocations in these systems?**

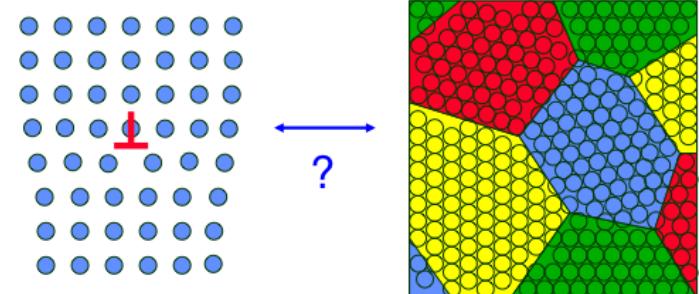
## **Our approach:**

Understand structural relationships between chalcogenide phases.

Determine basic elements of interfacial structure.

## **Dislocations and Interfacial Line Defects:**

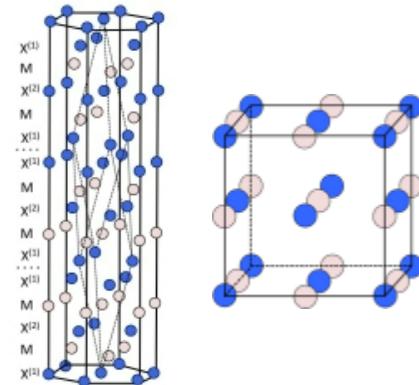
Building blocks to general understanding of interface structure and behavior.



# Outline

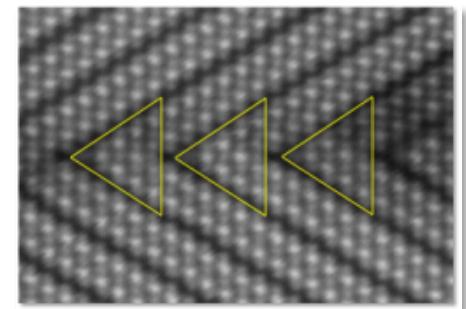
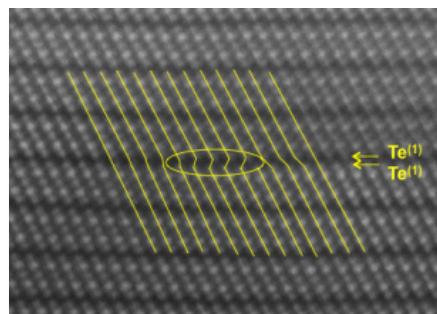
- **Crystal structure in tetradymite-type compounds**

- Layered structure gives flexibility in accommodating compositional variations
- Close structural relationship to rock-salt chalcogenides



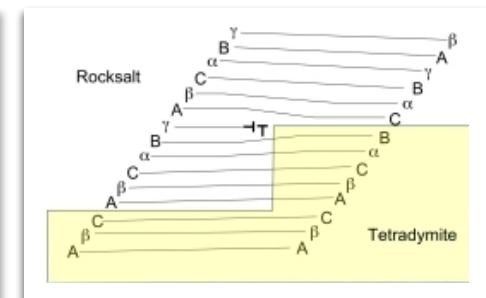
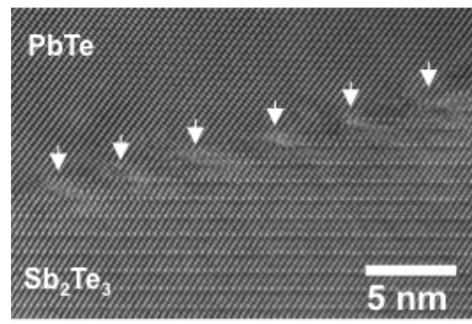
- **Dislocation and Grain Boundary Structure in  $Bi_2Te_3$**

- Impact of weak interlayer bonding
- local rock-salt coordination

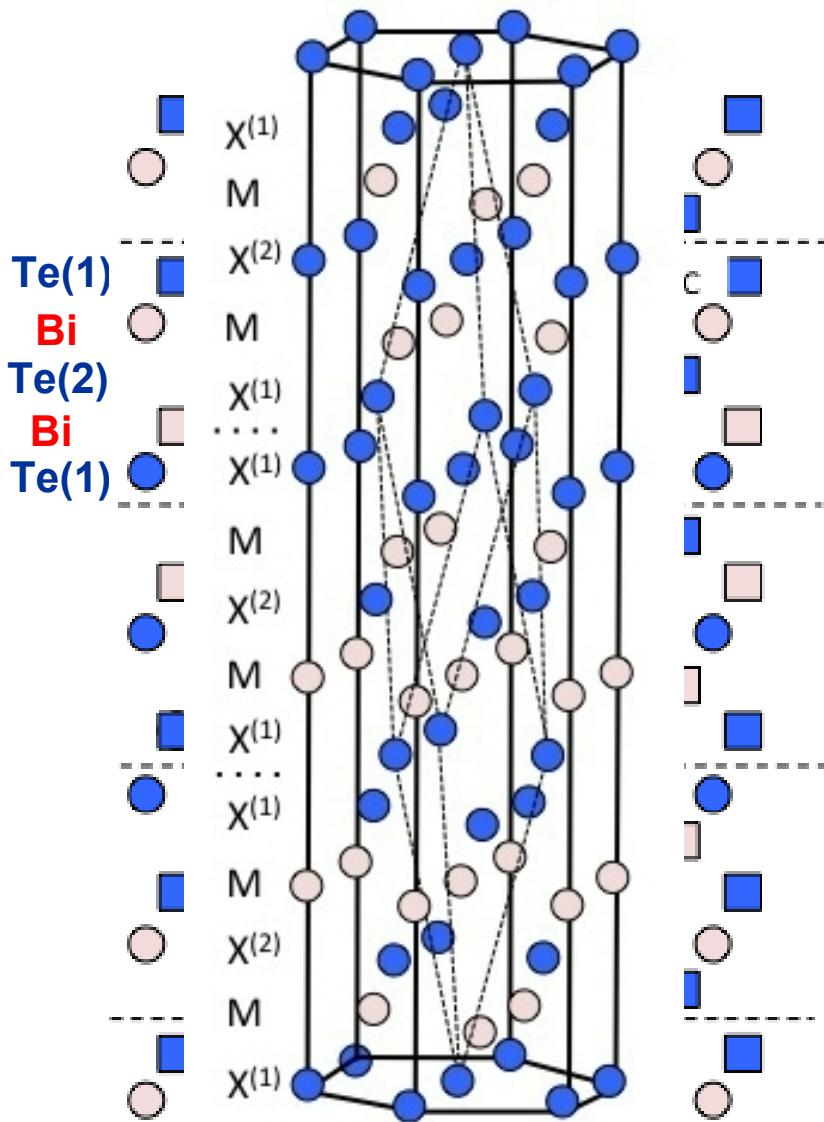


- **Rocksalt/Tetradymite heterophase interfaces:**

- Interfacial disconnections at  $Sb_2Te_3$  precipitates in  $AgSbTe_2$ , and  $PbTe$ .
- Defect roles in mechanisms for phase transformation and strain accommodation

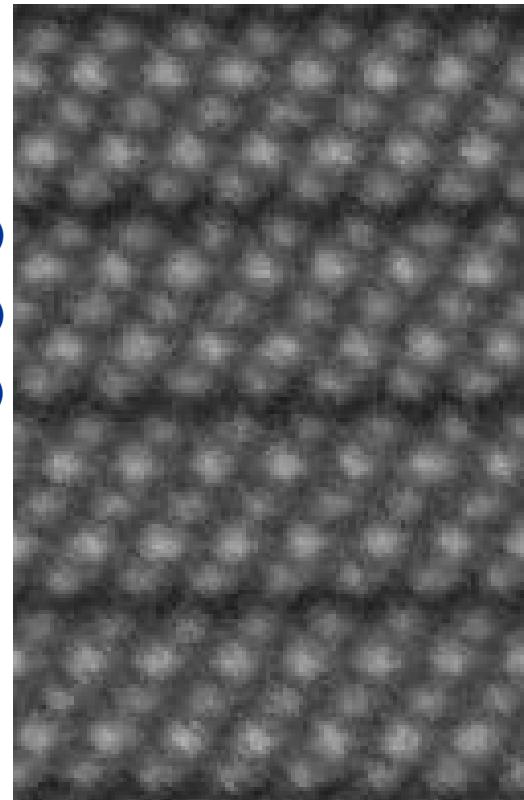


# Bismuth Telluride ( $\text{Bi}_2\text{Te}_3$ ): Crystal Structure



- Rhombohedral (R-3m) structure
- Based on tetradymite ( $\text{Bi}_2\text{STe}_2$ ) prototype
- Three crystallographically distinct atomic sites
- $\text{Te}^{(1)}\text{-Te}^{(1)}$  layers: van der Waals bonding

HAADF-STEM



Bi:  $Z=83$   
Te:  $Z=52$

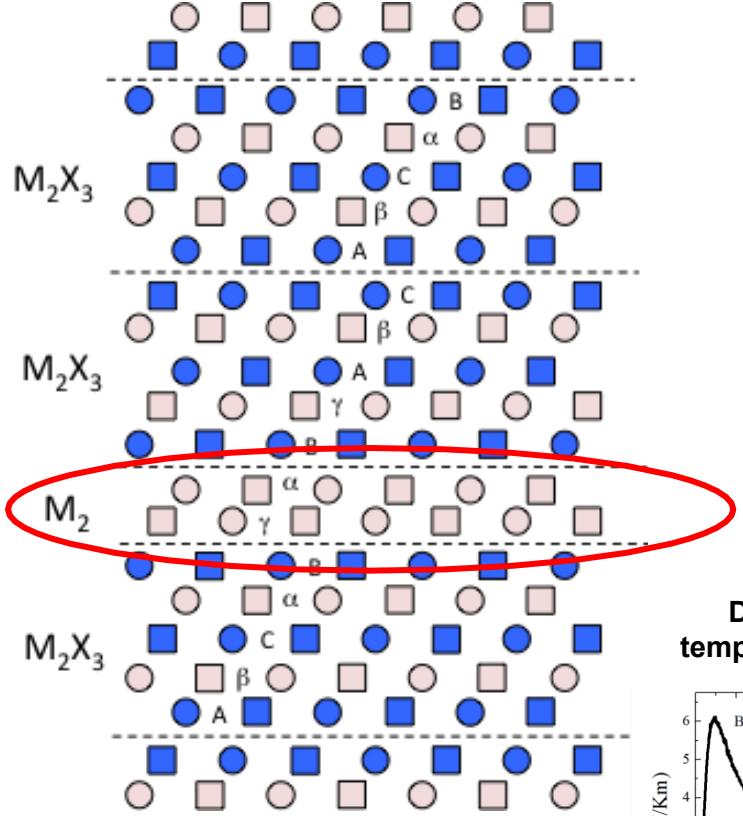
Atomic number difference enables Bi and Te to be distinguished in HAADF-STEM



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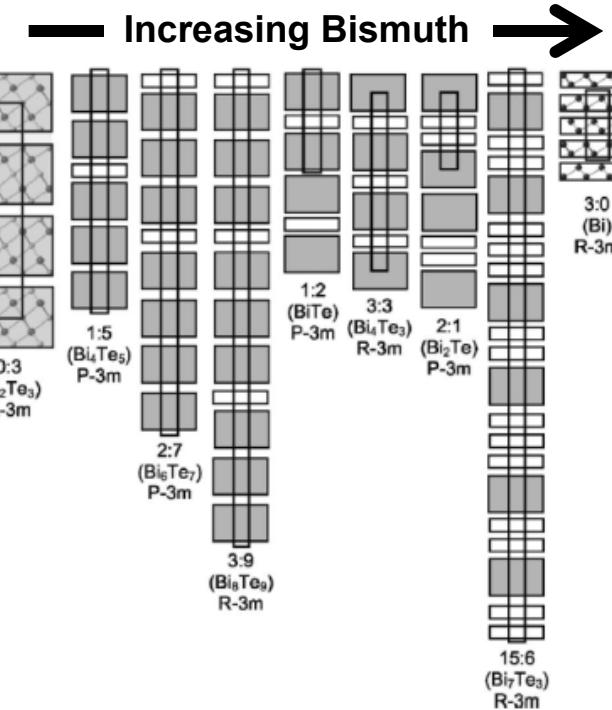
# Layered structure allows flexibility in accommodating variations in composition

## Insertion of metal bi-layers

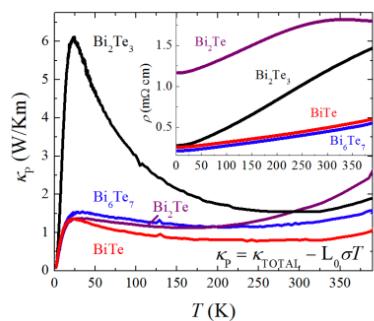


Example:  
 $(Bi_2)_m(Bi_2Te_3)_n$   
 homologous series

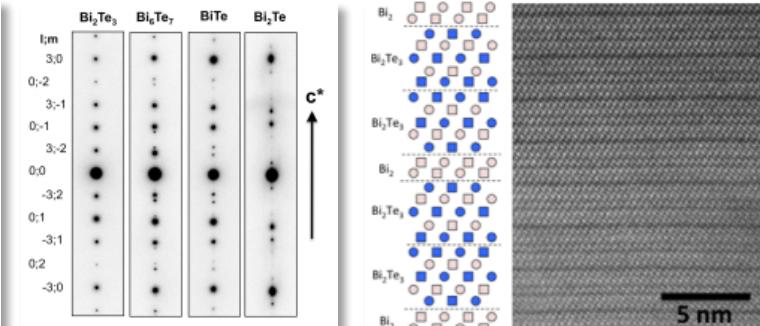
J.W.G. Bos, H.W.  
 Zanderbergen,  
 M.-H. Lee, N.P. Ong,  
 R.J. Cava,  
 Phys. Rev B 2007



Dramatic reduction in low-temperature thermal conductivity

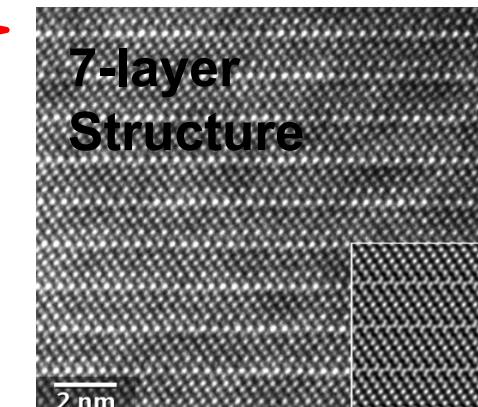
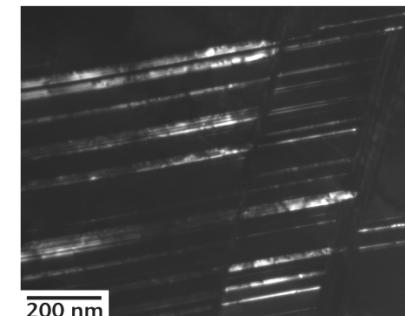
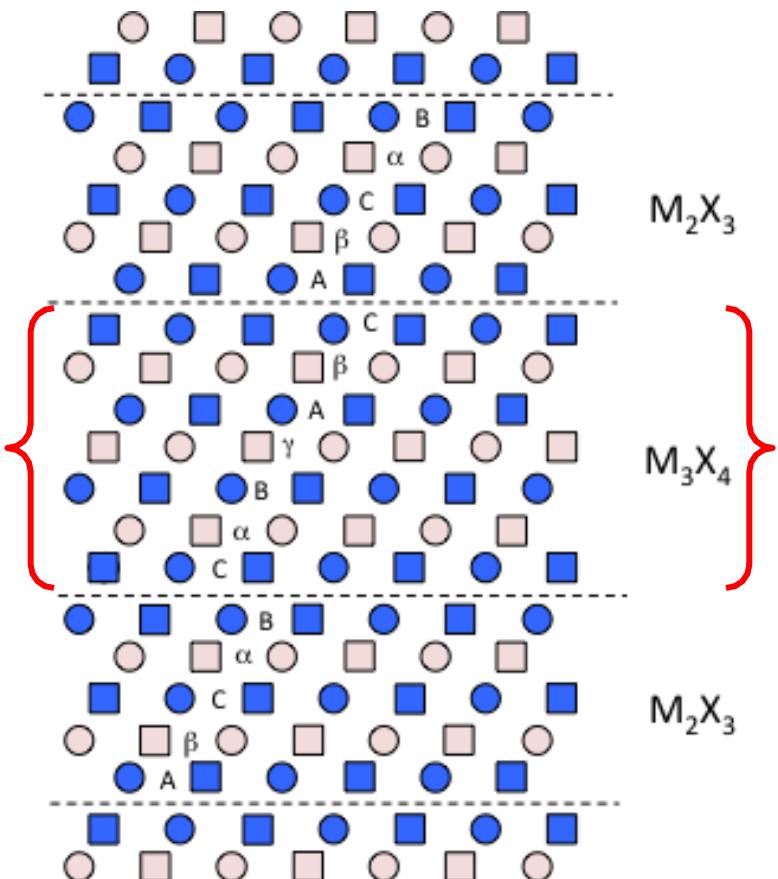


Electron diffraction and HRSTEM show ordering in  $(Bi_2)_m(Bi_2Te_3)_n$  series

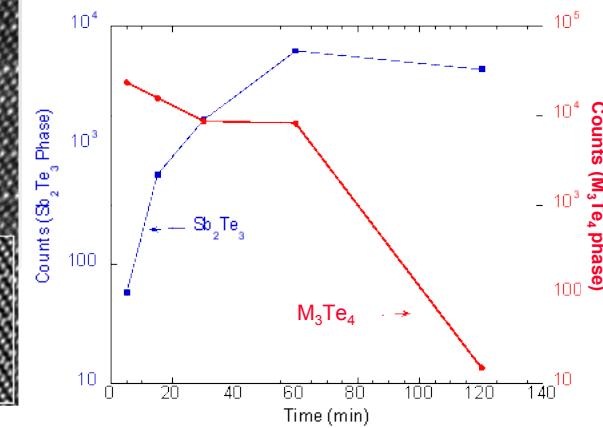
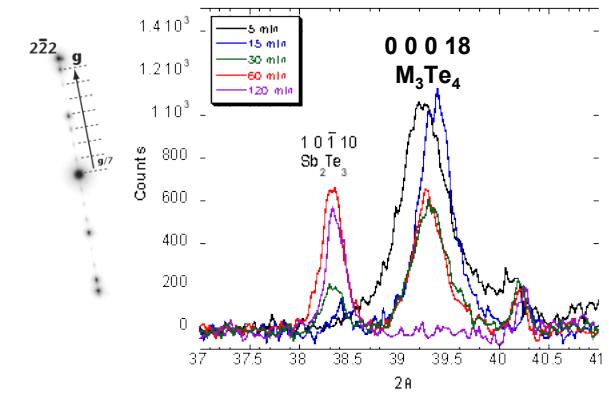


# Layered structure allows flexibility in accommodating variations in composition

Metal rich, 7-Layer  $M_3X_4$  fault



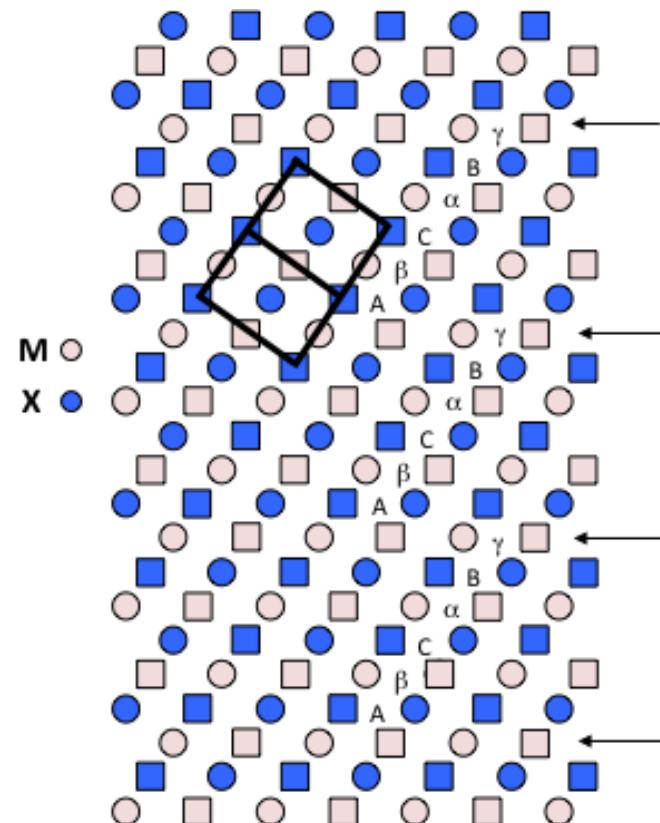
Example:  $(Ag,Sb)_3Te_4$  transition phase during nucleation of  $Sb_2Te_3$  precipitates in  $AgSbTe_2$



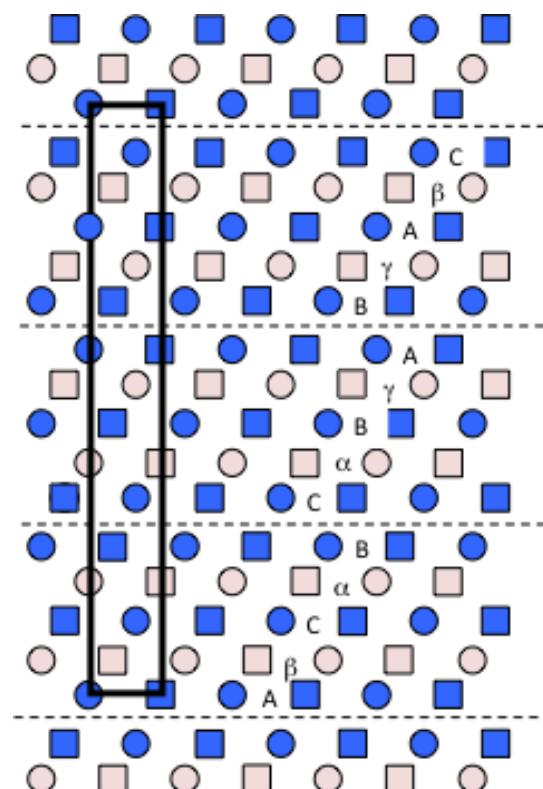
Sharma, Sugar, & Medlin, Journal of Applied Physics (2010).  
Sugar and Medlin, Journal of Materials Science (2011)

# Tetradymite and Rocksalt structures are closely related

Rocksalt (MX) Structure

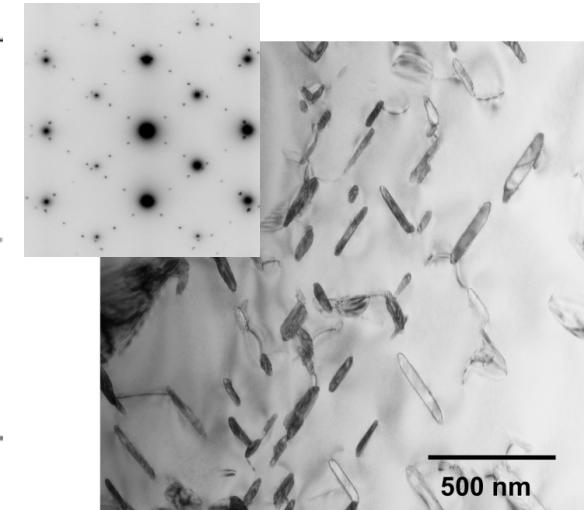


Tetradymite ( $M_2X_3$ ) Structure



Example:

Crystallographically Aligned  
 $Sb_2Te_3$  precipitates in PbTe

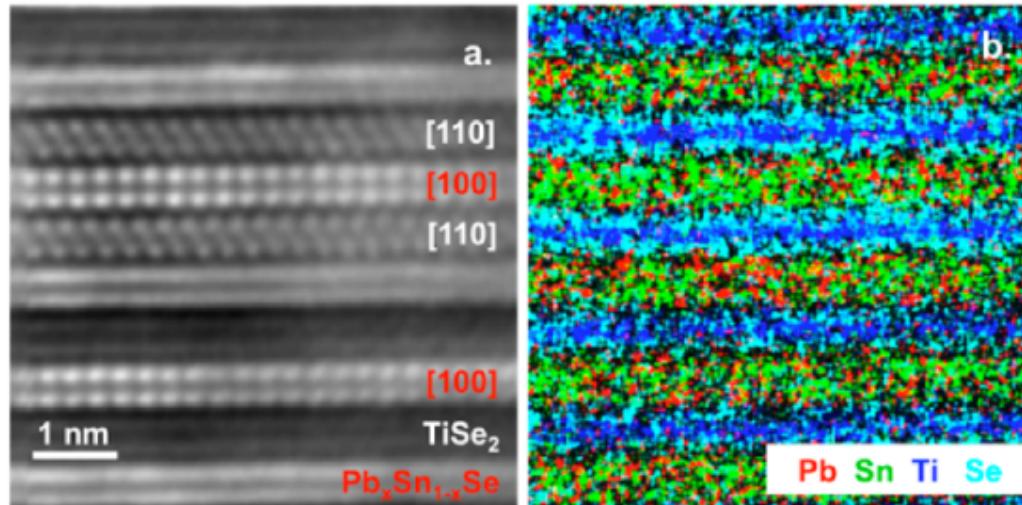
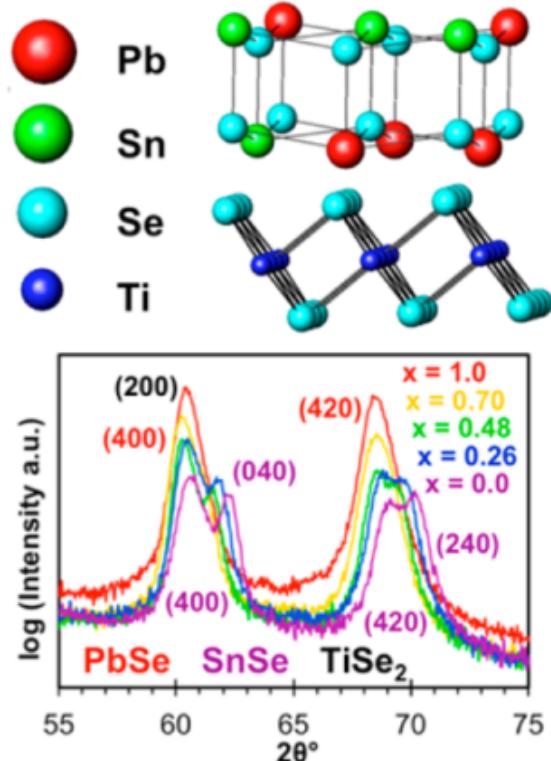


Heinz, Snyder, Ikeda, and  
Medlin, Acta Mat. 2011

- Solid-state phase transformations in chalcogenides
- Structural interpretation of extended defects

# Layered Chalcogenides: Diversity of Compositional and Structural Arrangements

## Example: $(\text{Pb}_x\text{Sn}_{1-x}\text{Se})_{1+\delta}\text{TiSe}_2$ Intergrowth Compound



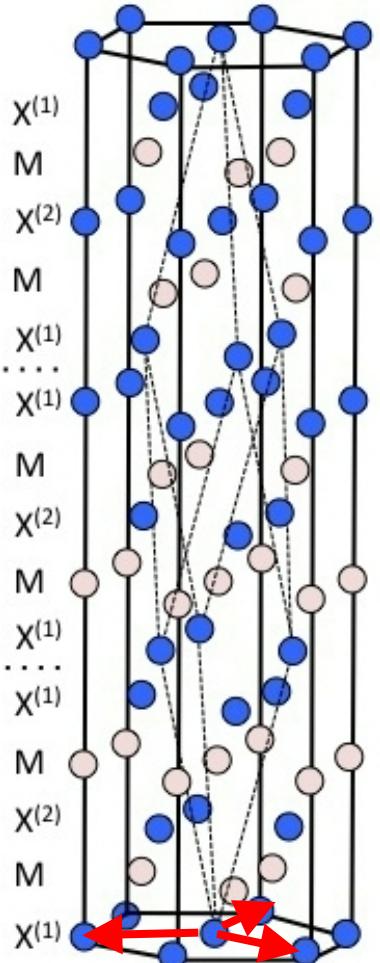
- Site specific alloying:
  - Sn, Pb on "rocksalt" bilayers
  - Separated by  $\text{TiSe}_2$  tri-layers
- Crystalline sheets, but rotational, "turbostratic," disorder between layers
  - a "ferecrystal"

FEI-Titan 80-200  
Chemistem

# How do these structural considerations impact Dislocations and Interfaces?

## *Dislocations in Bismuth Telluride*

Burgers vectors lying in basal plane



Array of  $1/3<2-1-1\ 0>$  Dislocations in  $\text{Bi}_2\text{Te}_3$

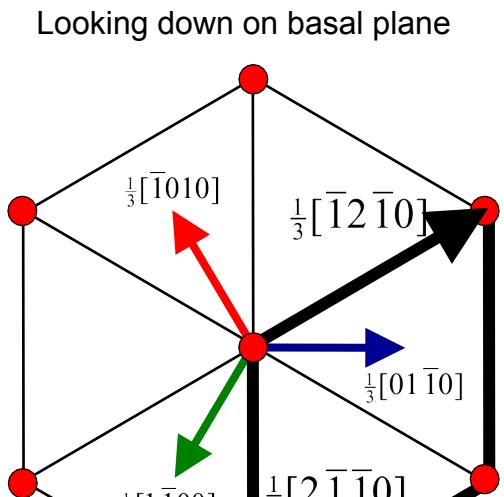
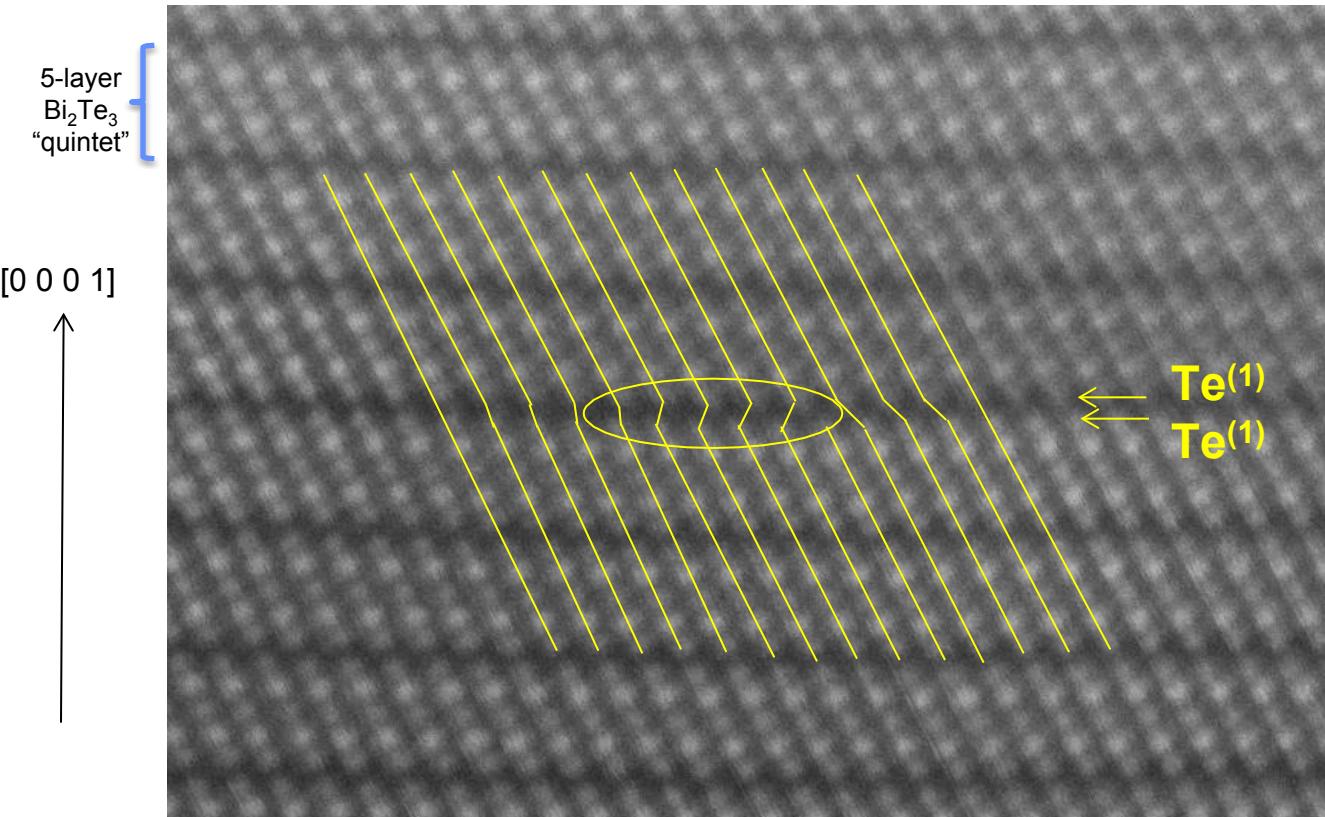


Fig. 1. Dislocation network in  $\text{Bi}_2\text{Te}_3$ . Note that certain segments of dislocations and certain node-points have left the foil

# Dislocation Core structure: termination at Te<sup>(1)</sup>-Te<sup>(1)</sup> layer, core spreading



$b=1/3<2 -1 -1 0>$

60° mixed dislocation

Dissociated?

Stacking Fault  
30° mixed partial

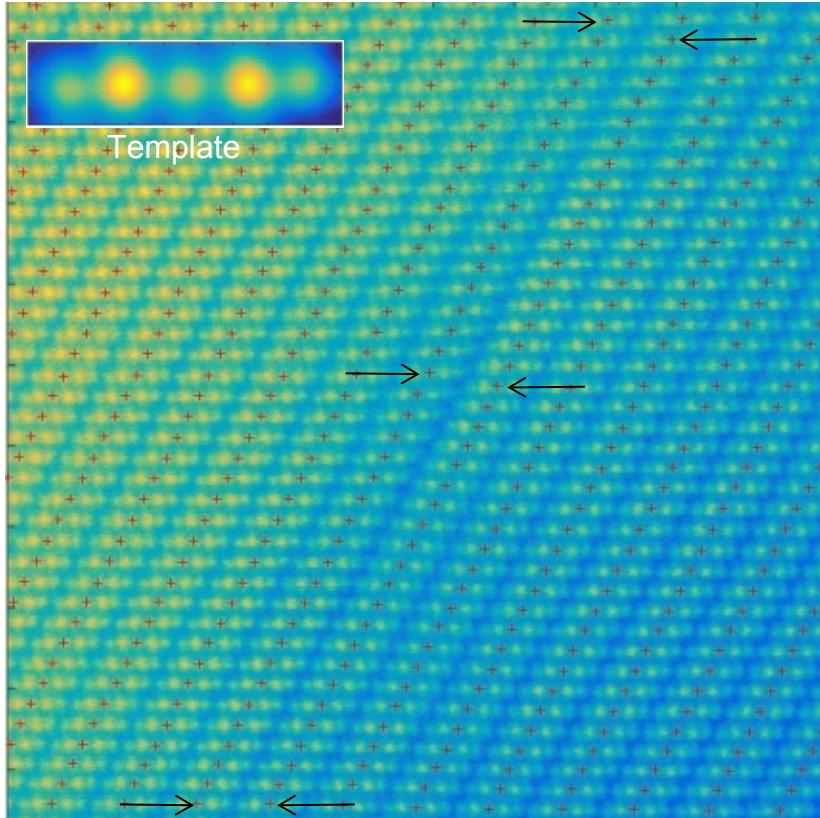
90° edge partial

$1/3<1 0 -1 0>$  partial dislocations.

FEI-Titan  
HAADF-STEM  
300 keV

# Quantify Disregistry on Slip Plane using Peierls-Nabarro Dislocation Model

Disregistry of  $\{1\ 0\ -1\ 5\}$  planes across slip plane measured through template matching

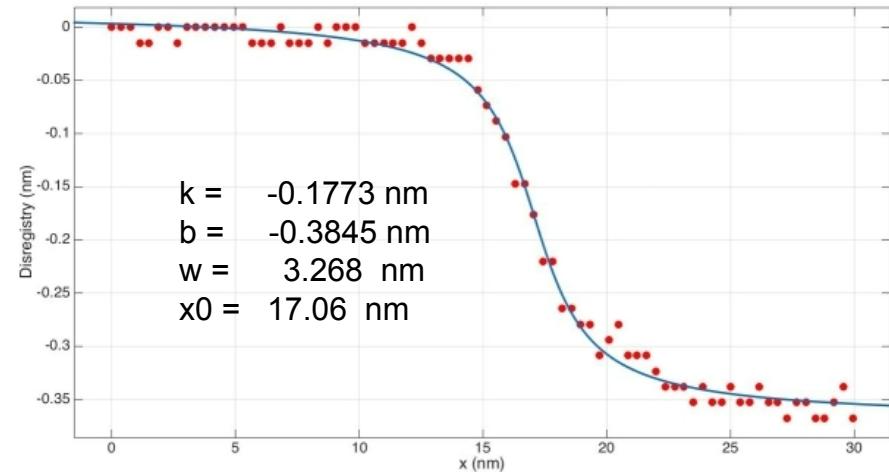


$$w = 3.7 \text{ nm} \pm 0.6 \text{ nm}$$

6 dislocations  
2-4 measurements each

$$u_+ - u_- = k + \frac{b_{edge}}{\pi} \tan^{-1} \left( \frac{x - x_0}{w/2} \right)$$

Disregistry      Burgers vector      core-width

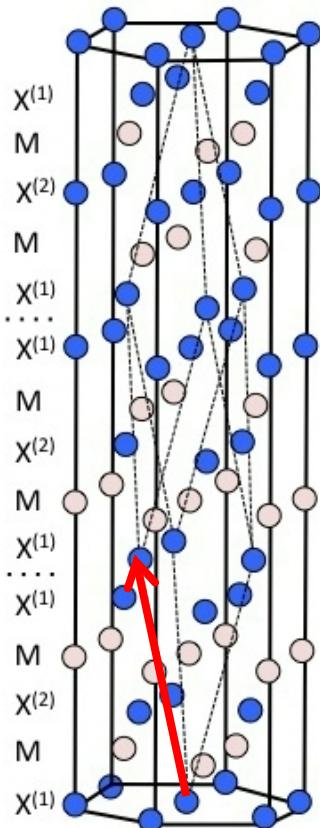


Core-spreading on basal plane, but no localized partial dislocations or well defined stacking fault.

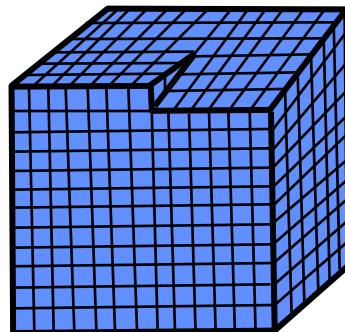
Working with modelers to extract energetics of gamma-surface.

# Non-basal dislocations:

## *Screw dislocations important to crystal growth*

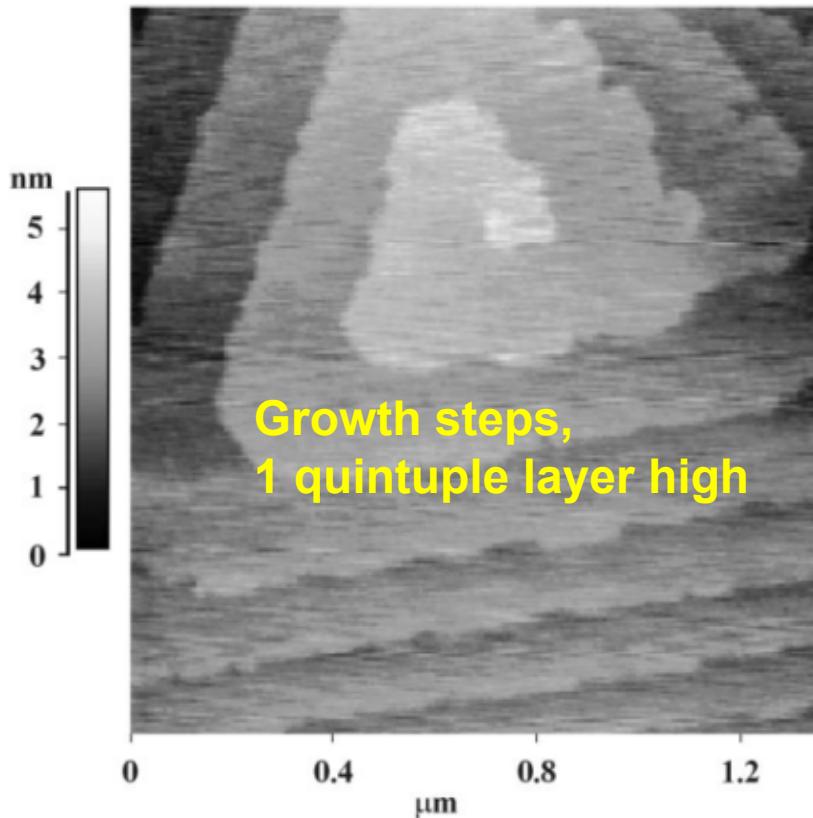


Screw Dislocation



$$\mathbf{b} = (1/3)[0-111]_H = [001]_R$$

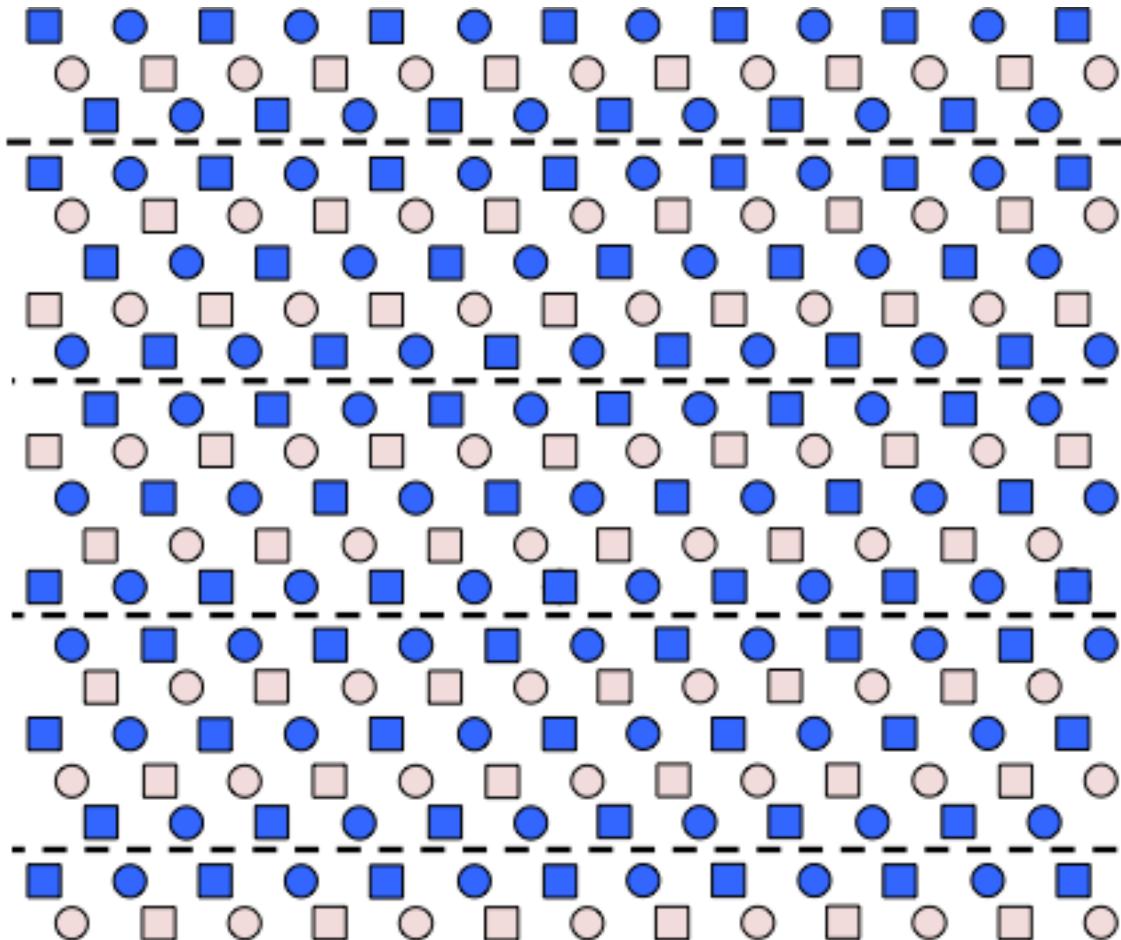
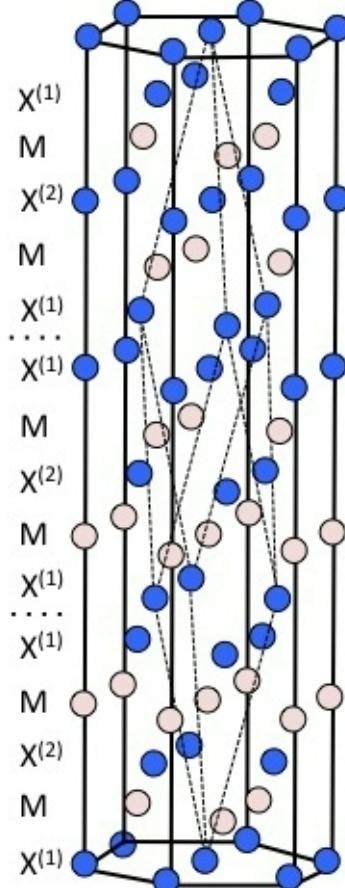
Example: spiral growth steps at screw dislocation in  $\text{Bi}_2\text{Te}_3$  thin film



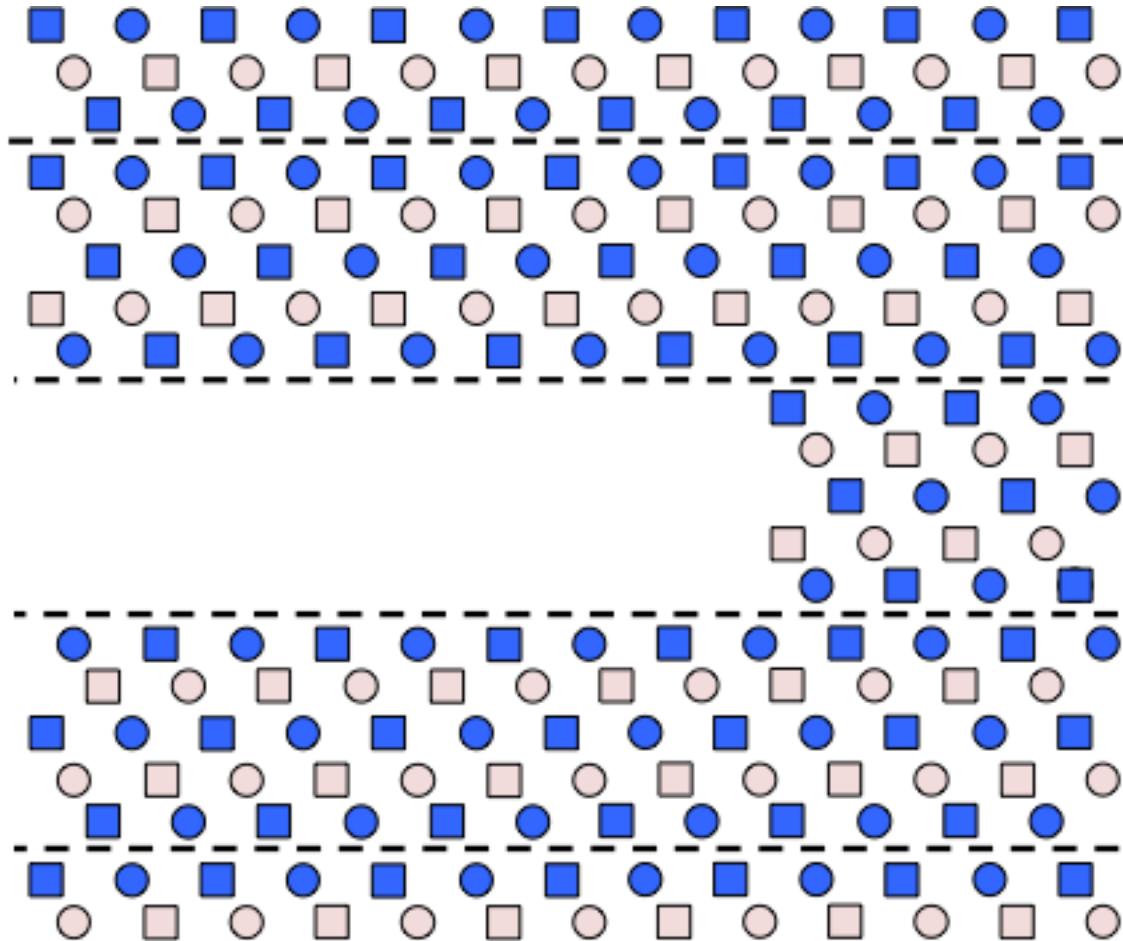
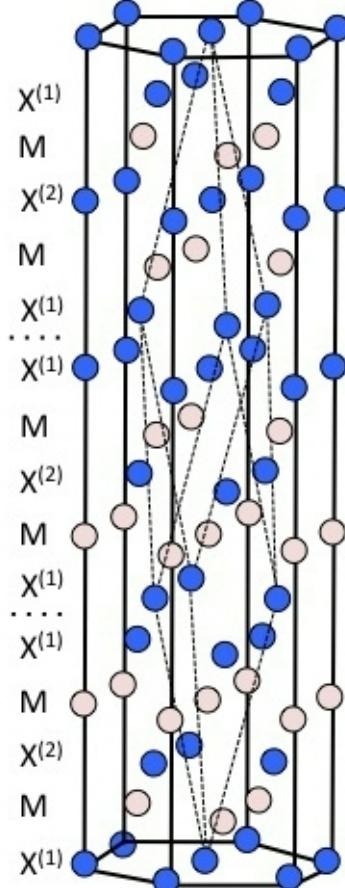
What about **edge** dislocations with non-basal Burgers vectors?

M. Ferhat, J.C. Tedenac, J. Nagao,  
J. Crystal Growth (2000)

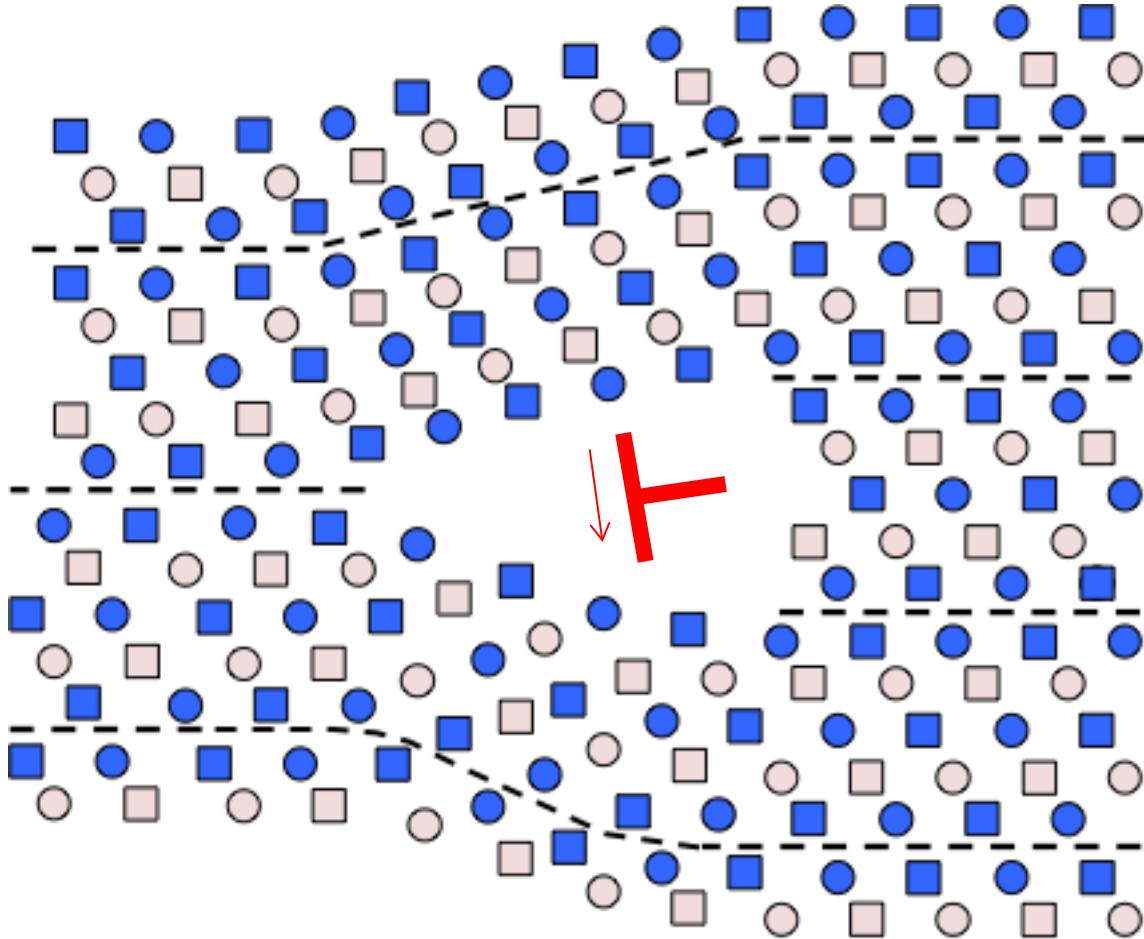
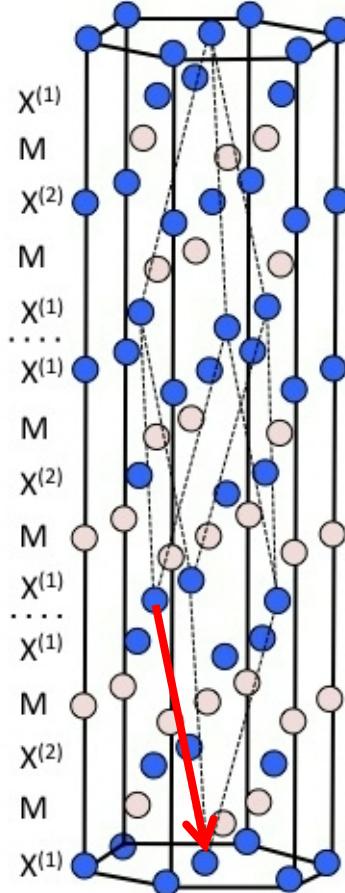
# Non-basal edge dislocations: What happens if we pull out a quintuple unit?



# Non-basal edge dislocations: What happens if we pull out a quintuple unit?

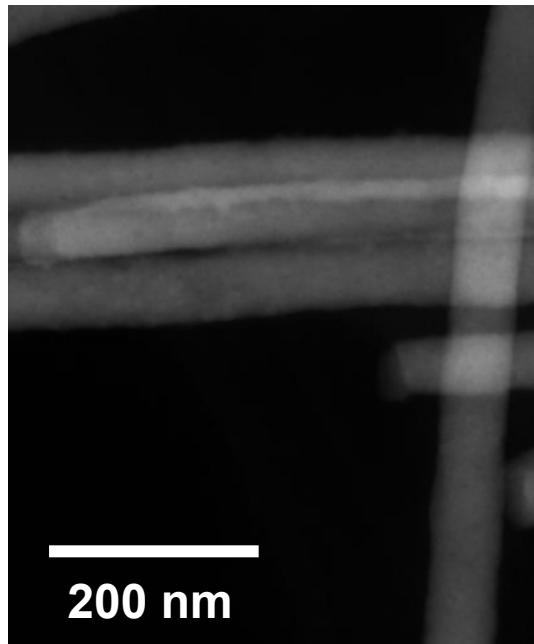


# Non-basal edge dislocations: What happens if we pull out a quintuple unit?



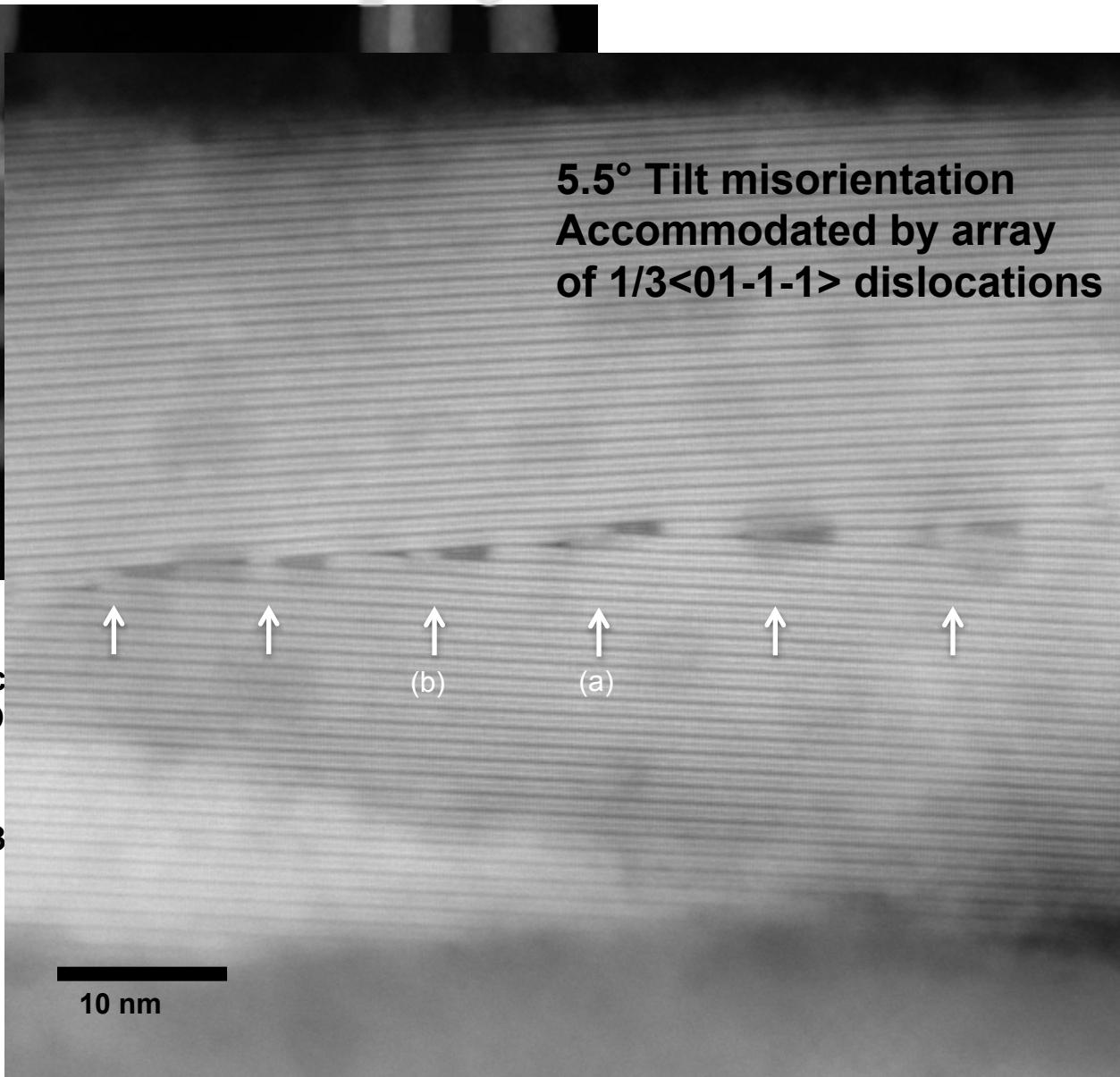
$$\mathbf{b} = (1/3)[01-1-1]_H = [00-1]_R$$

# Dislocations in $\text{Bi}_2\text{Te}_3$ Nanowires

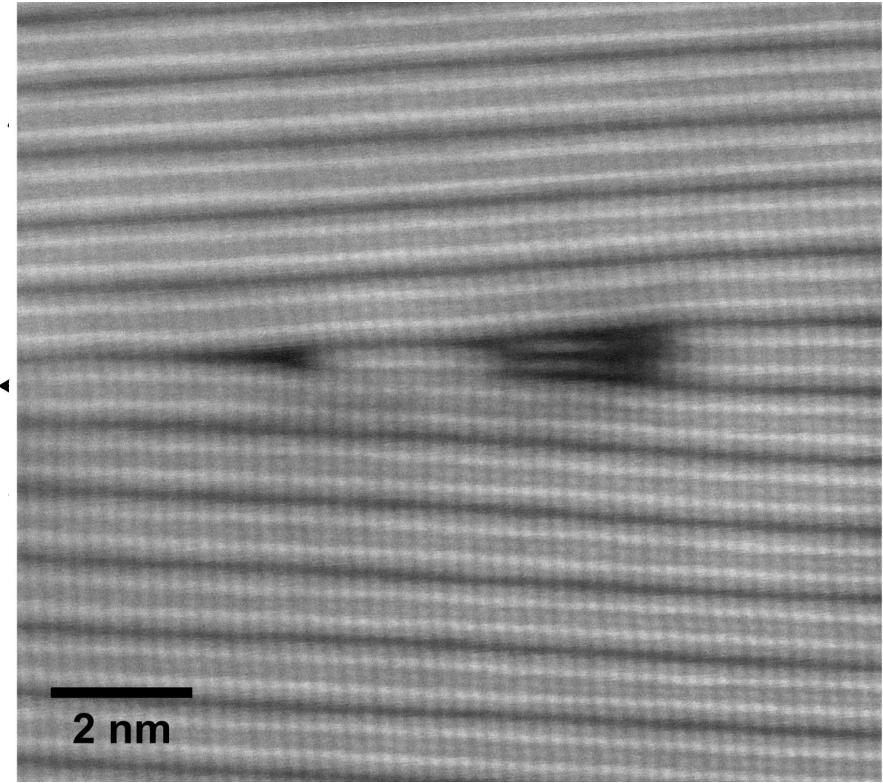
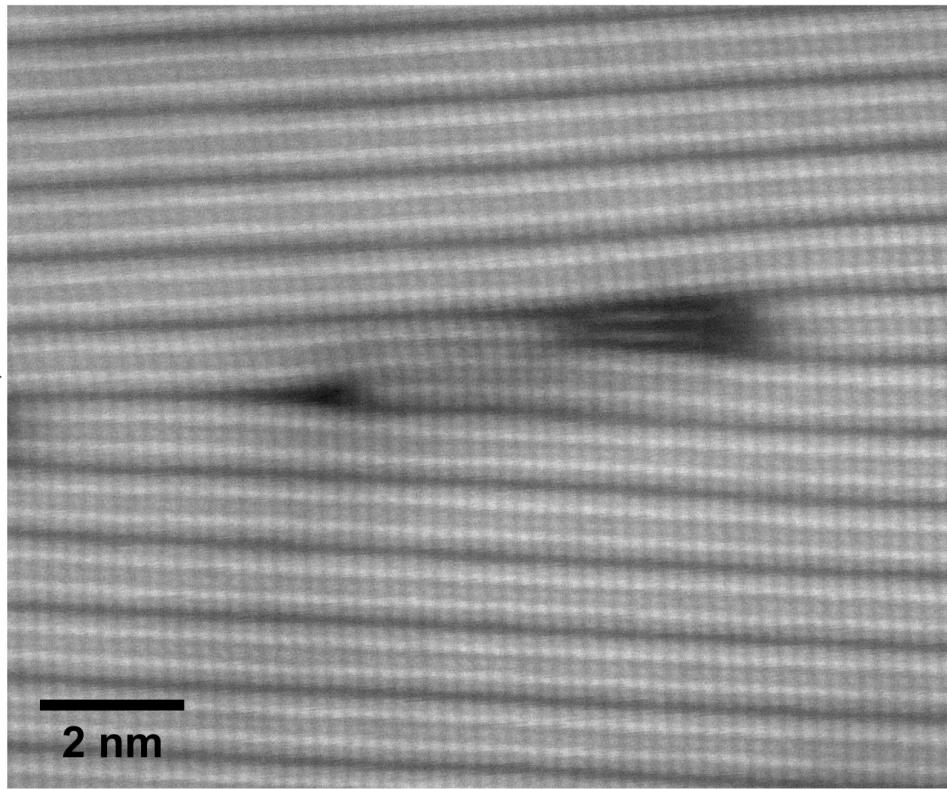


Wires formed by electrochemical deposition in nanoporous AAO templates.

Free standing wires annealed 3 minutes at 300°C in Ar-3%H<sub>2</sub>.

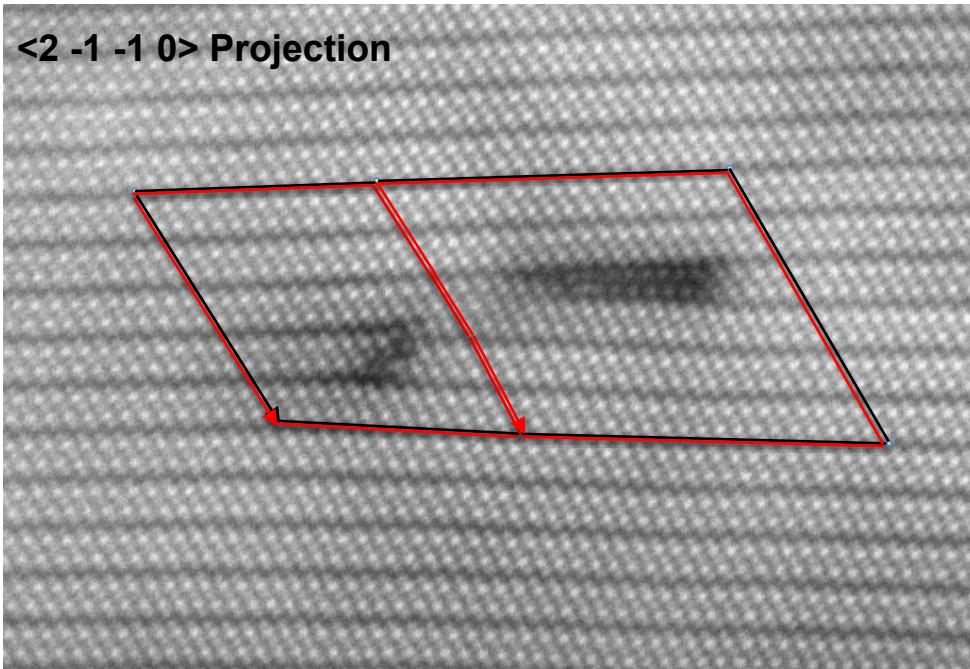


# Dislocations have dissociated core: two configurations

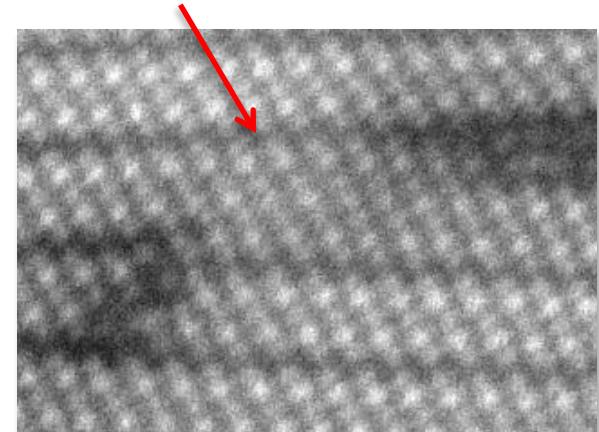


$<1\ 0\ -1\ 0>$  Projection

# $(1/3)[0\ 1\ -1\ -1]$ Dislocation in $\text{Bi}_2\text{Te}_3$ :



Core structure:  
 $\text{Bi}_3\text{Te}_4$  7-layer fault



$$\mathbf{b} = (1/3) [0\ 1\ -1\ -1] \rightarrow (1/15) [0\ 5\ -5\ -2] + (3/15) [0\ 0\ 0\ -1]$$

$$\mathbf{b}^2 > \mathbf{b}_1^2 + \mathbf{b}_2^2$$
$$109.8 \text{ \AA}^2 > 22.9 \text{ \AA}^2 + 37.2 \text{ \AA}^2 = 60.2 \text{ \AA}^2$$

*Reduced strain energy with dissociation*

# 7-Layer $Bi_3Te_4$ faults: Mechanism to accommodate Te loss during annealing

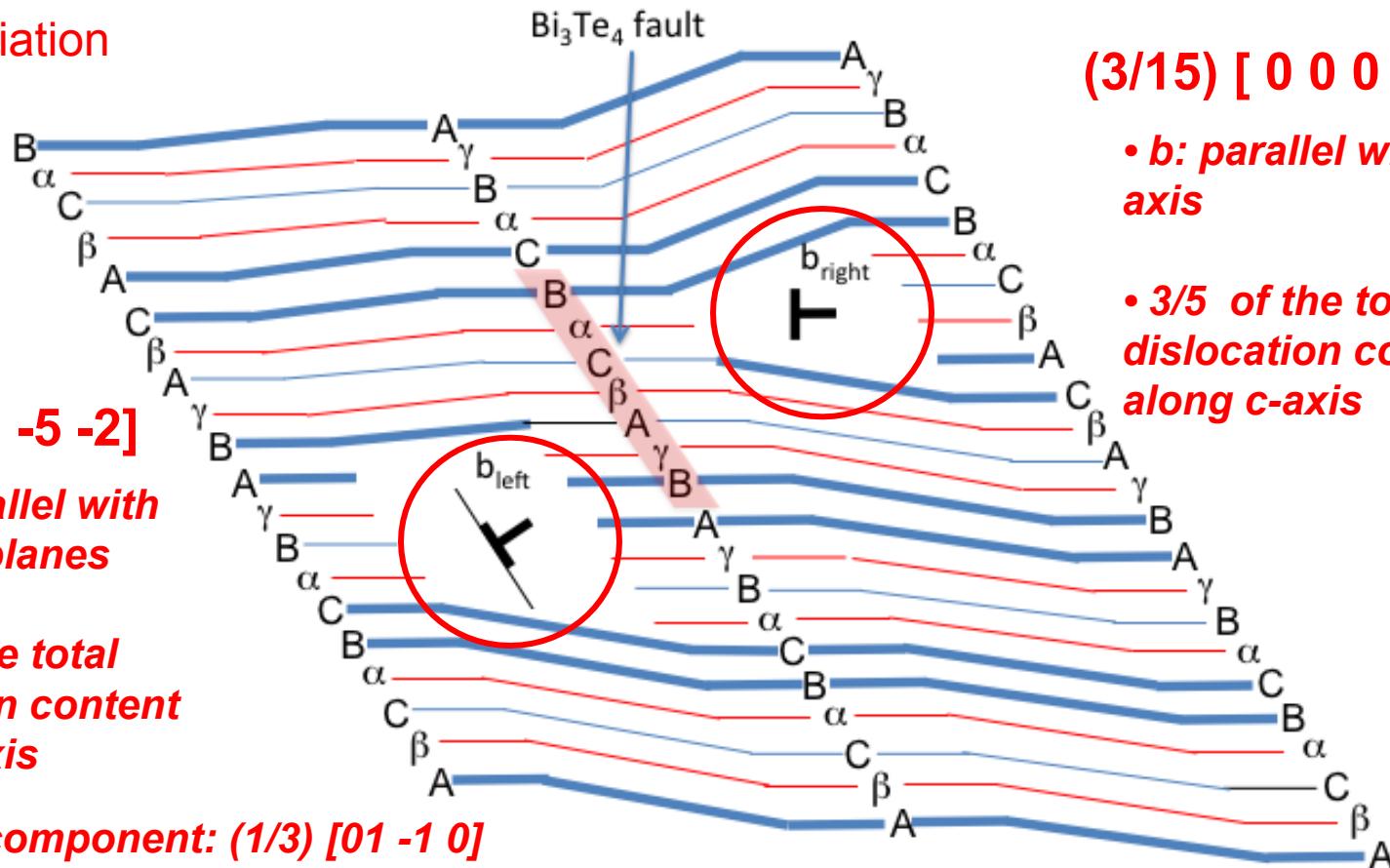
Climb dissociation

(1/15) [0 5 -5 -2]

- $b$  is parallel with  $(0\ 1\ -1\ 5)$  planes
- 2/5 of the total dislocation content along  $c$ -axis

Horizontal component: (1/3) [01 -1 0]

- analogous to Shockley partial.
- avoids fault in stacking resulting from additional 2 planes at  $Bi_3Te_4$  fault



(3/15) [ 0 0 0 -1]

- $b$ : parallel with  $c$ -axis
- 3/5 of the total dislocation content along  $c$ -axis



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# Interfaces in the Tellurides

- Grain Boundaries:

- $\text{Bi}_2\text{Te}_3$

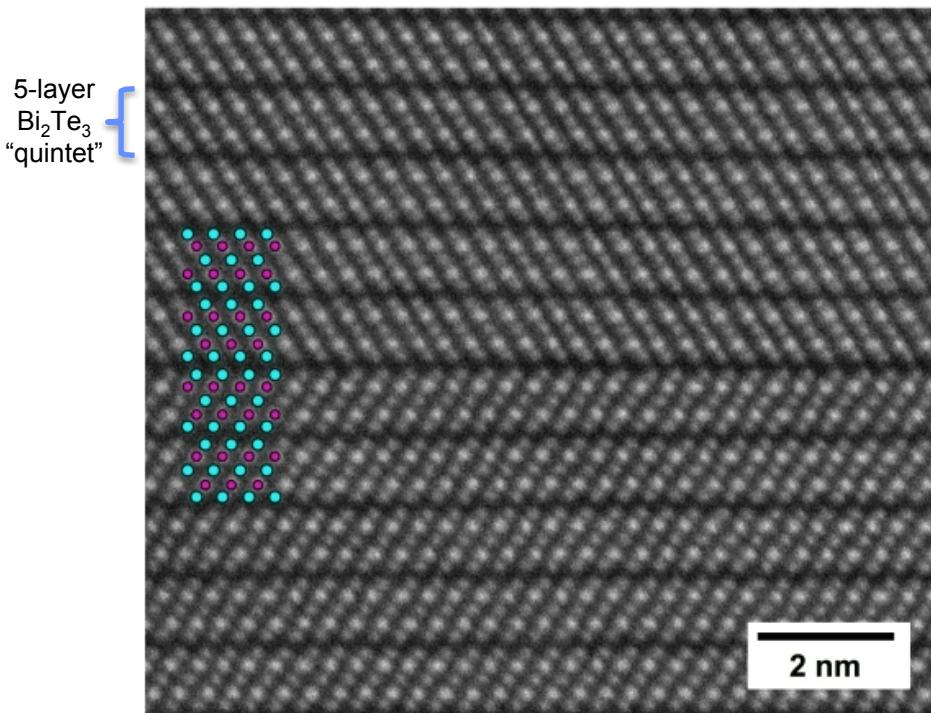
- Heterophase interfaces

- Rock salt / tetradymite

# Atomic Structure of the $\text{Bi}_2\text{Te}_3$ Basal Twin: Energetic preference for termination at $\text{Te}^{(1)}$ sites

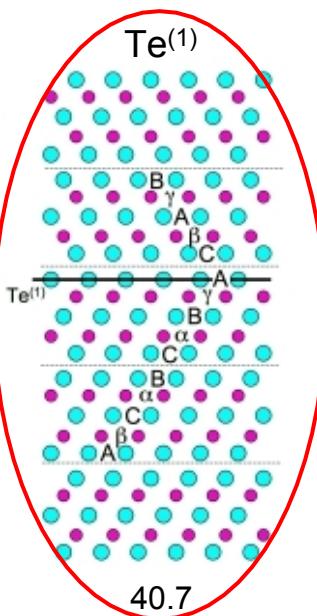
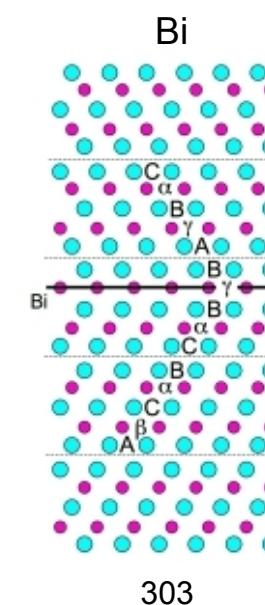
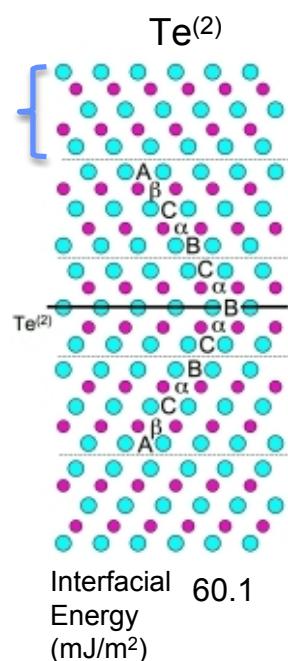
HAADF-STEM Imaging:

*Twin Boundary Terminated at  $\text{Te}^{(1)}$  layer*



DFT Calculations:

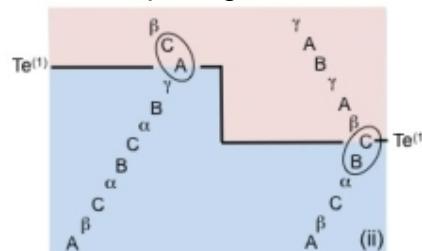
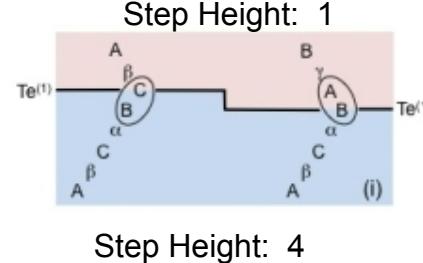
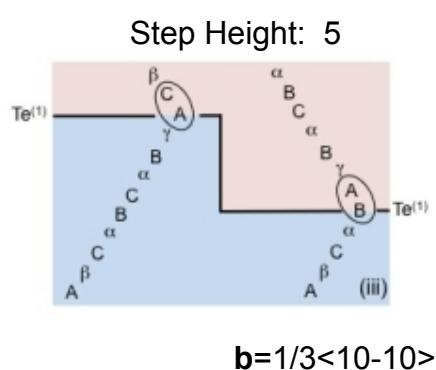
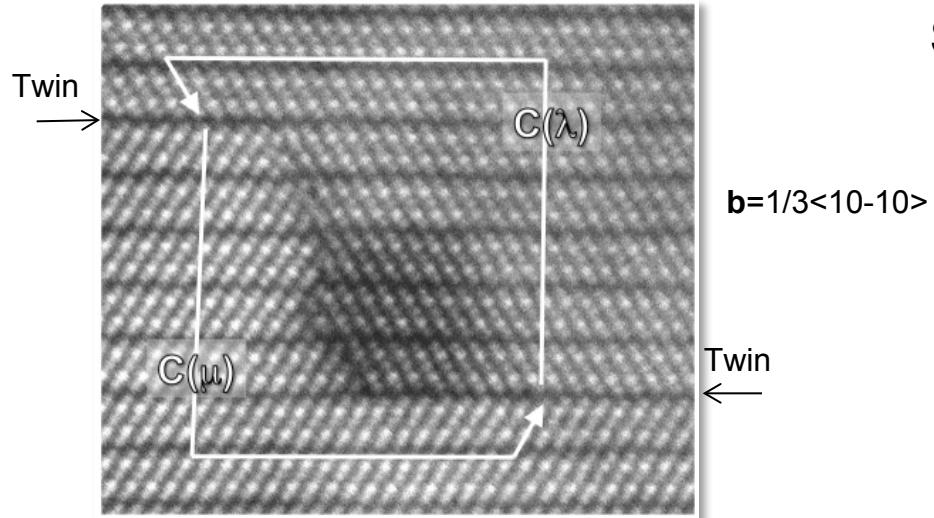
*Three Possible Compositional Terminations*



D.L. Medlin, Q.M. Ramasse, C. D. Spataru, N.C. Yang, J. Appl. Phys. (2010)

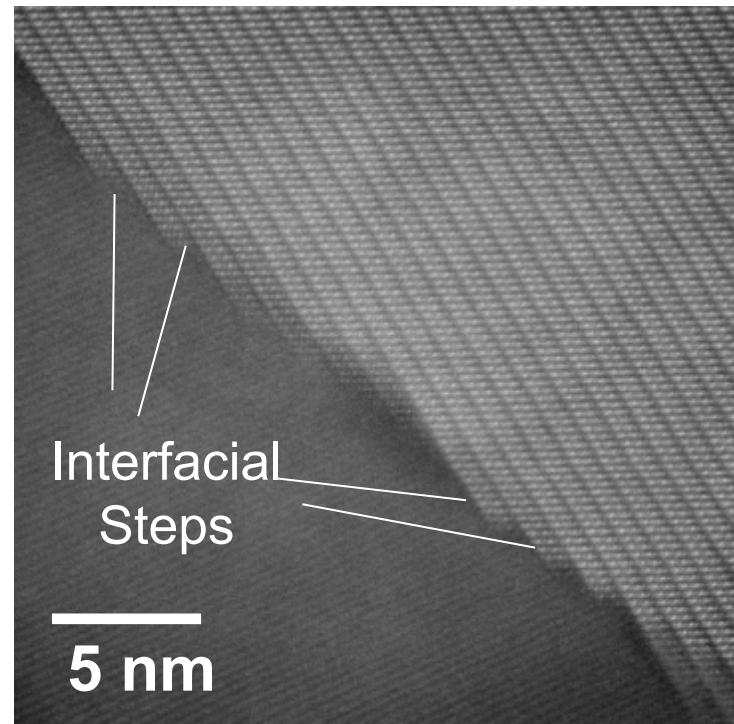
# Preferential termination at Te<sup>(1)</sup> layers: Impact on boundary steps

Example: step in Bi<sub>2</sub>Te<sub>3</sub> Basal Twin:  
25 planes high (5 quintets)



Medlin and Yang,  
Journal of Electronic  
Materials, (2012)

Grain boundary vicinal to (0001):  
Steps of integral 5-plane Bi<sub>2</sub>Te<sub>3</sub> Quintets

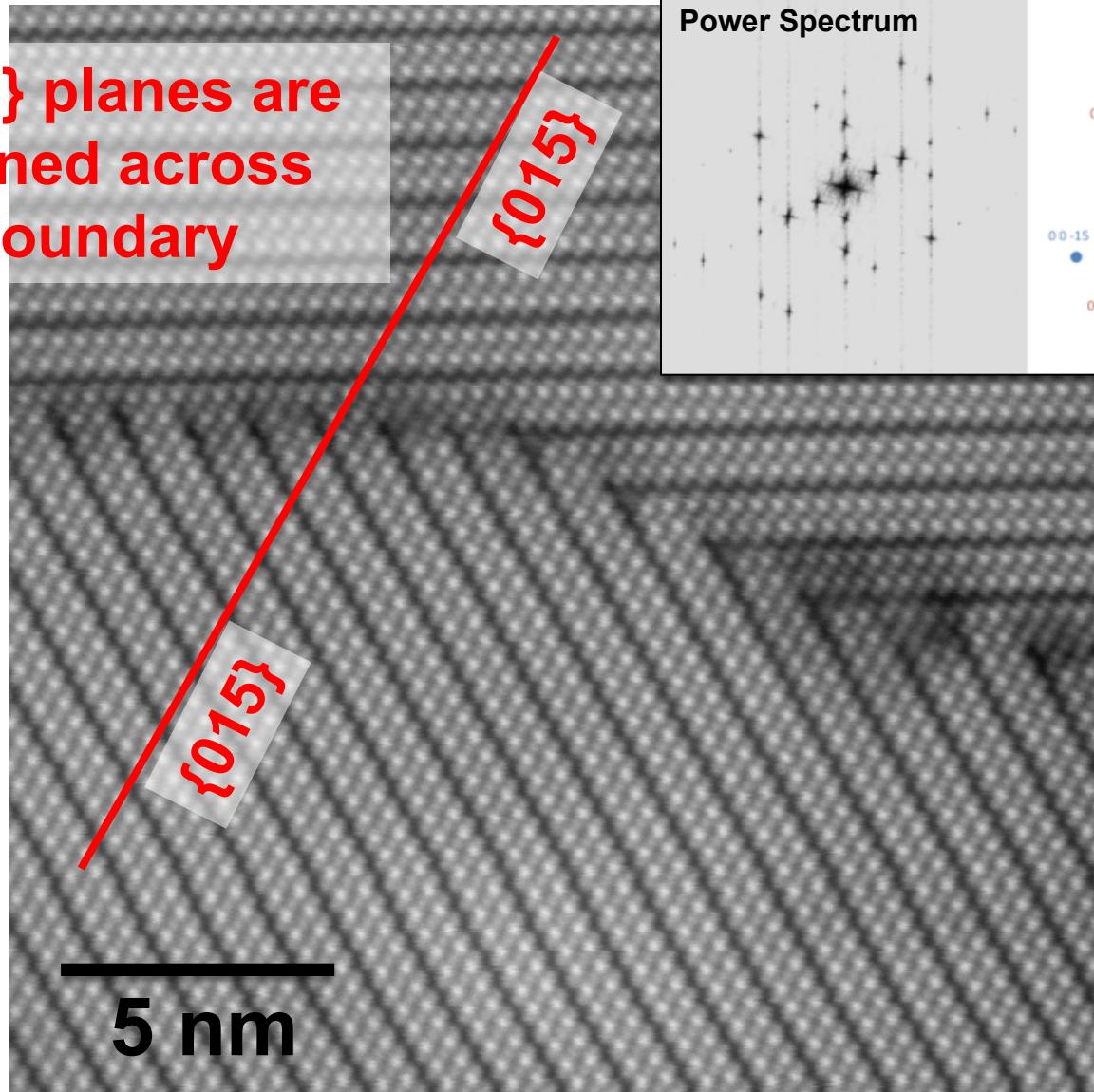


Medlin and Snyder,  
JOM (2013).

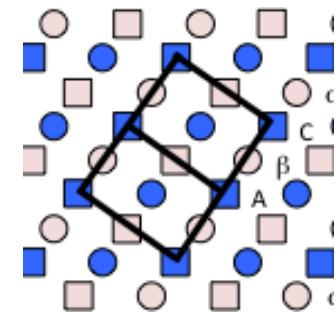
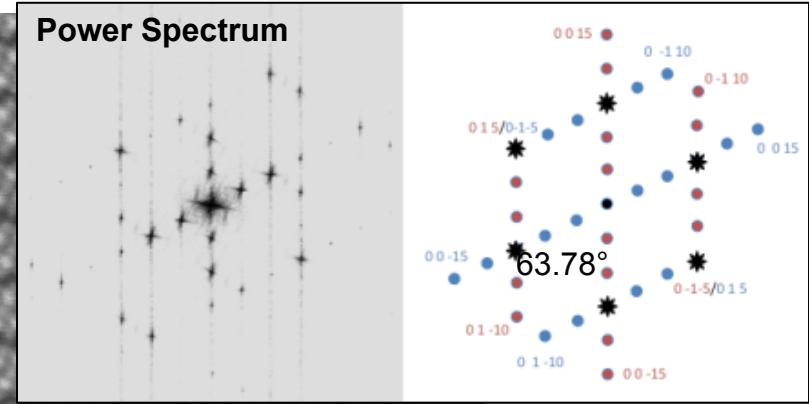
# $\text{Bi}_2\text{Te}_3$ $<2-1-1\ 0>/<-2\ 1\ 1\ 0>$ $63.78^\circ$ Boundary

Electrodeposited  
 $\text{Bi}_2\text{Te}_3$  nanowire  
Annealed 300°C

{015} planes are  
aligned across  
boundary



Power Spectrum



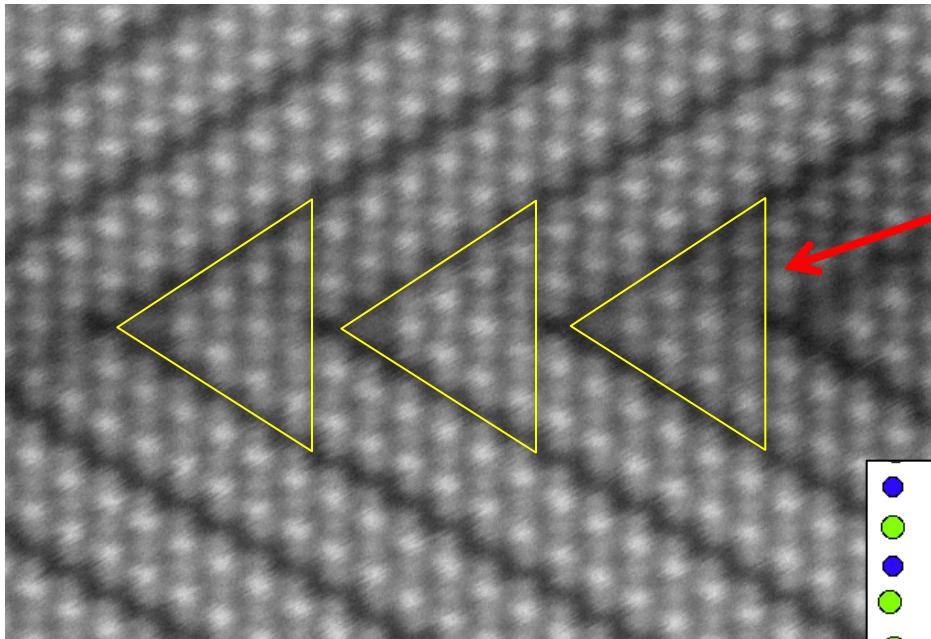
{015} planes  
in  $\text{Bi}_2\text{Te}_3$   
analogous to  
{100} planes  
in rocksalt

FEI-Titan  
HAADF-STEM  
300 keV

D.L. Medlin, S. Limmer, G. Yelton, M.P. Siegal, in preparation.

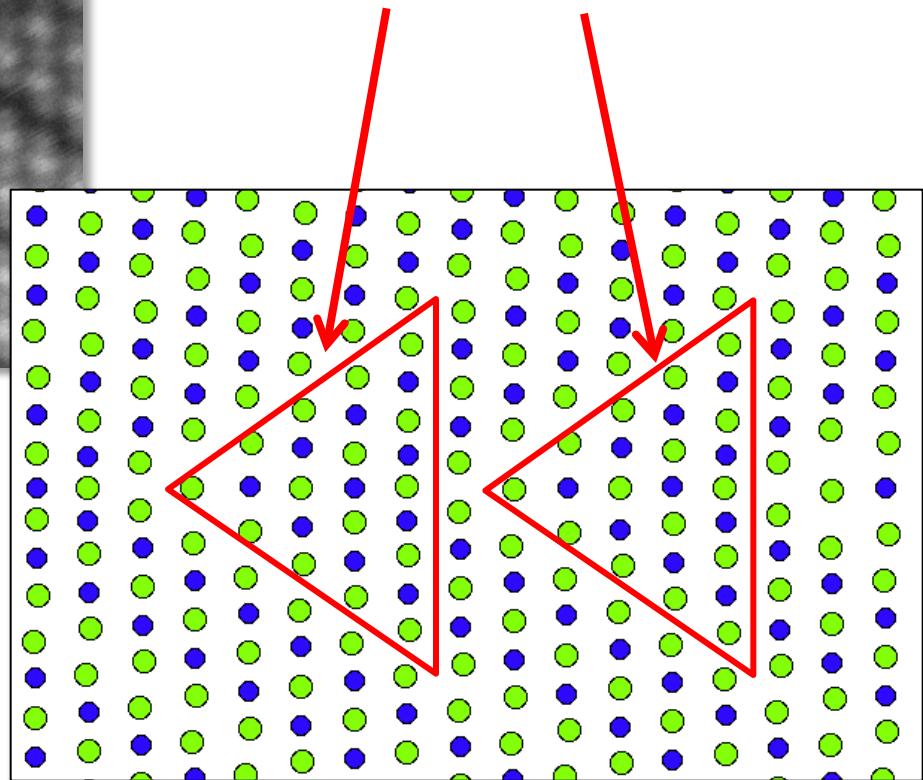
# Symmetrical Interface Configuration

(0,-1,1,13) interface inclination



*Rocksalt coordinated  
grain boundary units*

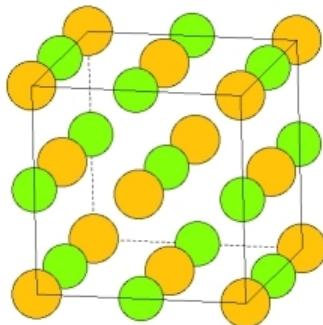
Each triangular unit:  
10 Bi 15 Te



2:3 ratio of Bi and Te maintained at interface

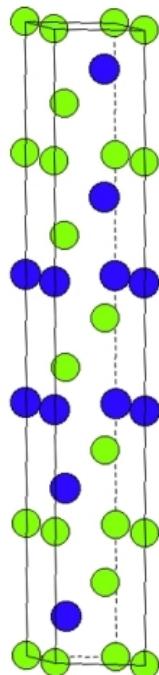
# Heterophase Rocksalt/Tetradymite Telluride Interfaces

**Rock-Salt**  
(PbTe, AgSbTe<sub>2</sub>)



Fm-3m

**Tetradymite**  
(Bi<sub>2</sub>Te<sub>3</sub>, Sb<sub>2</sub>Te<sub>3</sub>)



R-3m

**What happens at interface?**  
**How do transformations occur?**  
**Misfit accommodation?**

-Interest in forming thermoelectric nanocomposites of rock-salt and tetradymite tellurides:

- Possibility for well ordered interfaces.
- Transformations provide bulk route to synthesis.

Ikeda, et al., Chem Mater. 2007

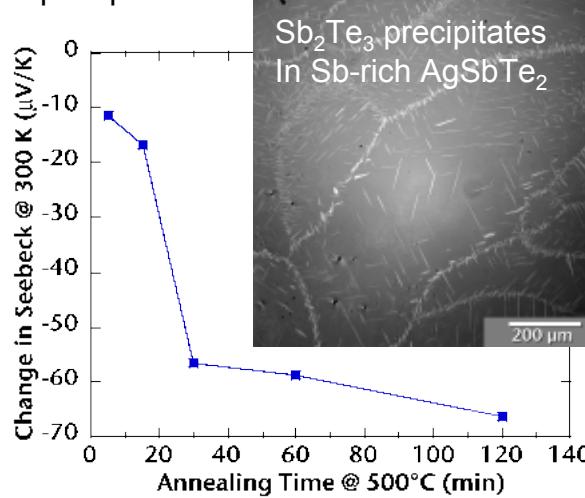
Snyder and Toberer, Nature Materials 2008

-AgSbTe<sub>2</sub>:

-Constituent of TAGS (GeTe)<sub>x</sub>(AgSbTe<sub>2</sub>)<sub>1-x</sub> and LAST (PbTe)<sub>x</sub>(AgSbTe<sub>2</sub>)<sub>1-x</sub> zT ~ 1.8

-High performance TE material: zT > 1.2

-Degradation of Seebeck coefficient with Sb<sub>2</sub>Te<sub>3</sub> precipitation



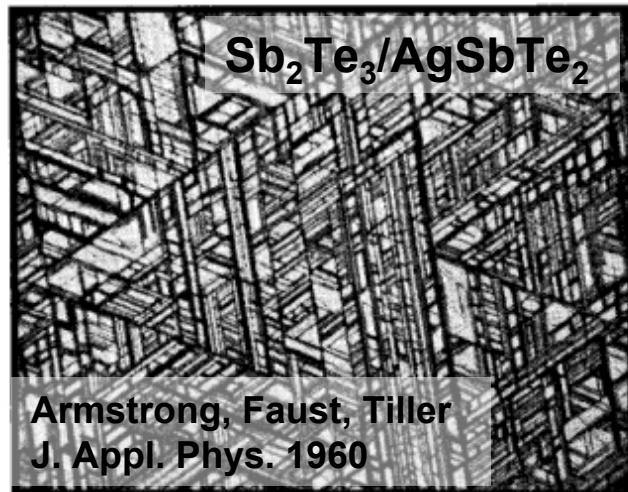
Sharma, Sugar, Medlin J. Appl. Phys. 2010



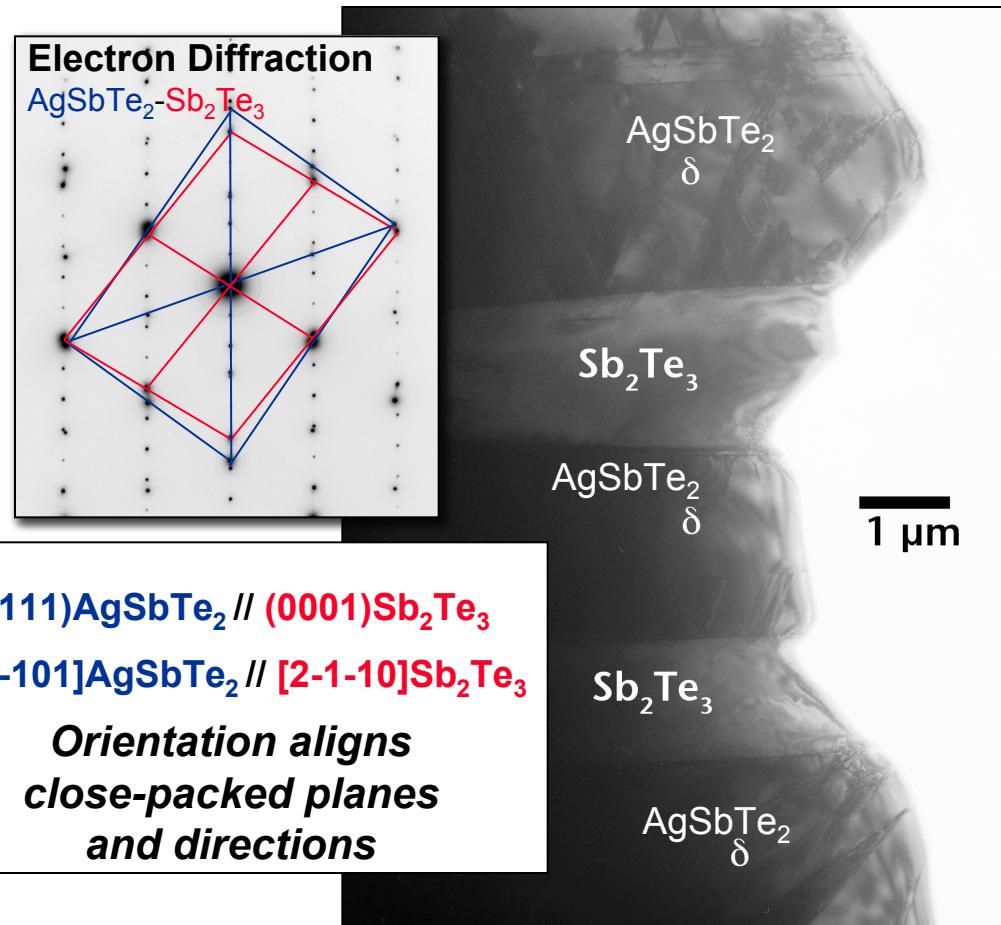
Sandia  
National  
Laboratories

# Crystallographic alignment between rocksalt and tetradyomite phases

Widmanstätten plates



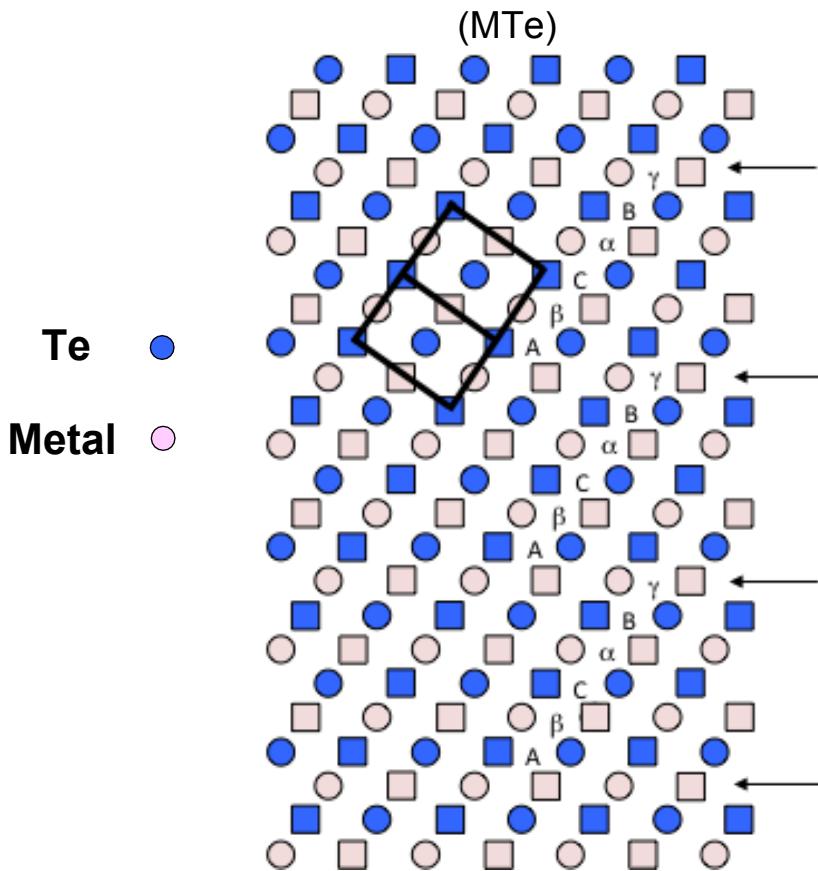
TEM Sb<sub>2</sub>Te<sub>3</sub>/AgSbTe<sub>2</sub>



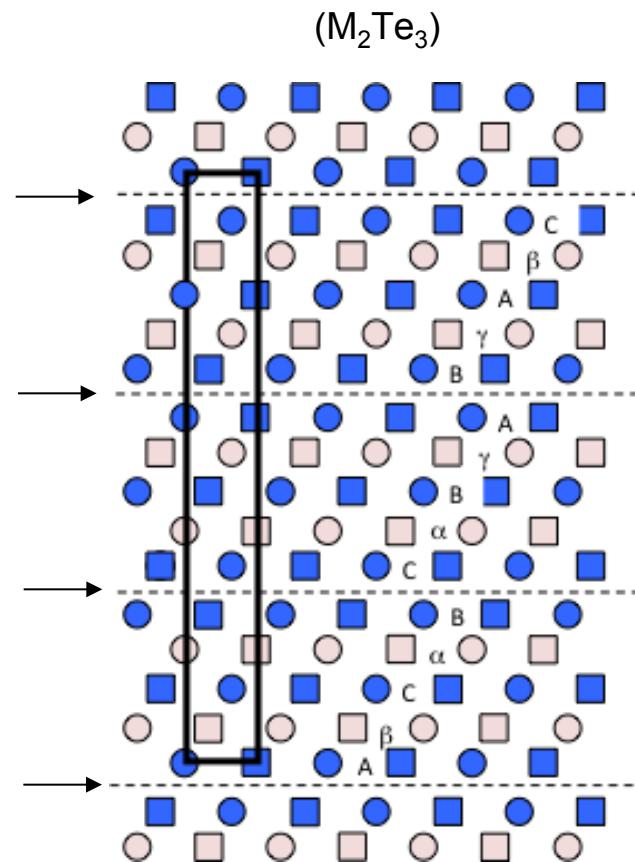
Medlin and Sugar,  
Scripta Mat 2010

# How to convert between the rocksalt and tetradyomite structures?

Rocksalt



Tetradyomite



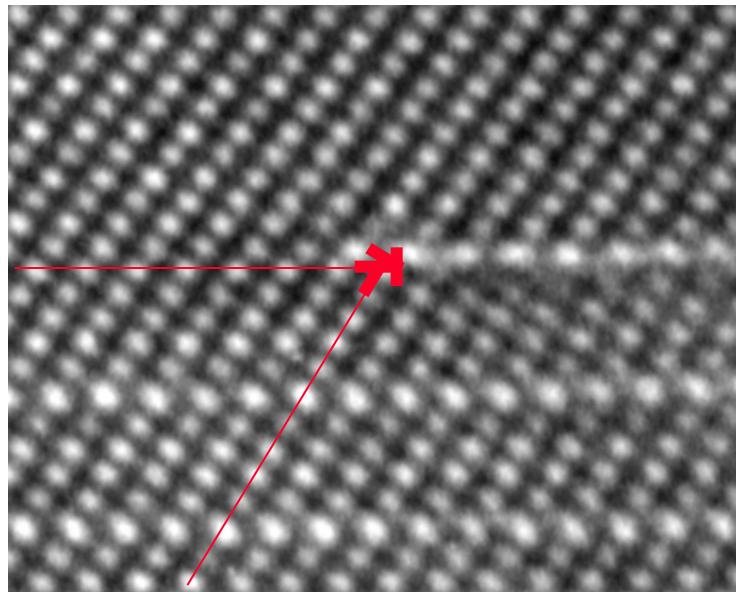
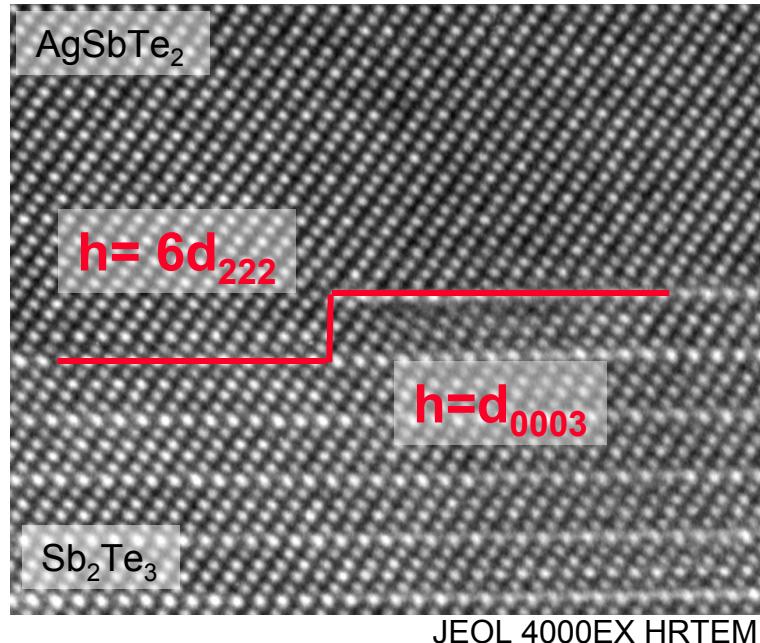
-Remove metal plane every 6 layers

-Shear blocks by  $1/3<10-10>$  (or  $1/6<112>$  relative to cubic coordinates)

N. Frangis et al., J. Solid State Chemistry 84 (1990)

**Transformation can be accomplished by motion of disconnections  
(steps with dislocation content)**

# HRTEM : Step at $\text{AgSbTe}_2/\text{Sb}_2\text{Te}_3$ Interface



*Defect has both **step** and **dislocation** character.*

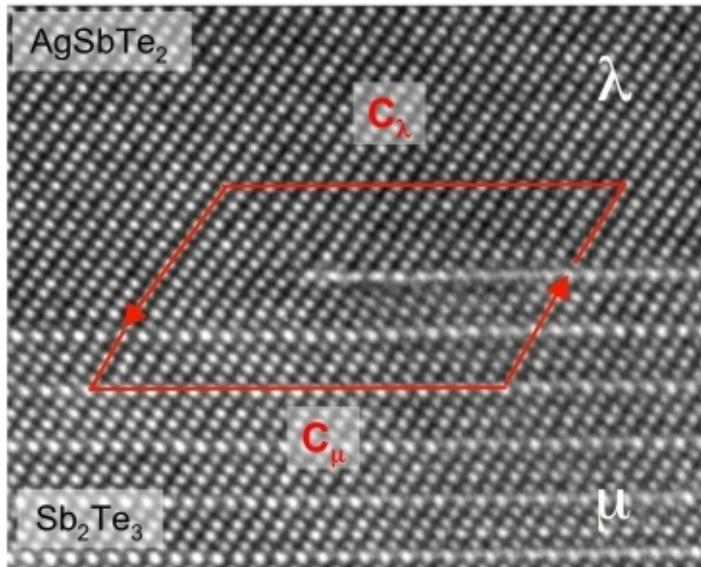
- Interfacial “Disconnection” (e.g. Hirth and Pond, Acta Mat 1996).
- Geometric properties of disconnections control mass flux and structural rearrangements of phase transformations.

*Step joins **6 {222} planes in  $\text{AgSbTe}_2$**  with **5 {000 15} planes in  $\text{Sb}_2\text{Te}_3$***

*Complex dislocation configuration.*

# Role of defect in precipitate growth:

Burgers vector:



Upper crystal circuit      Lower crystal circuit

$$\mathbf{b} = -(\mathbf{C}_\lambda + \mathbf{P} \mathbf{C}_\mu)$$

-Coordinate Transformation  
From Tetradymite to Rock-salt.  
-Coherently strained reference  
frame

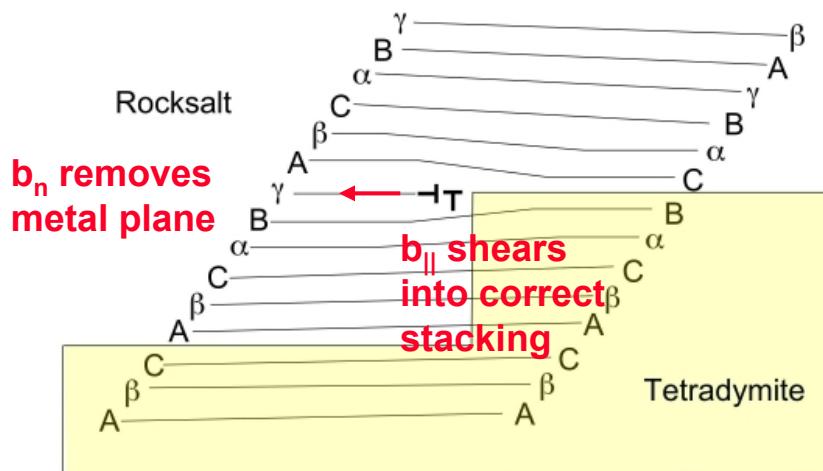
Resolve  $\mathbf{b}$  into components  
normal and parallel to interface

$$\mathbf{b}_n = (a_{cub} - c_{hex}/3\sqrt{3})[111]$$

- mismatch of step heights.
- $|\mathbf{b}_n| = 0.3747 \text{ \AA}$

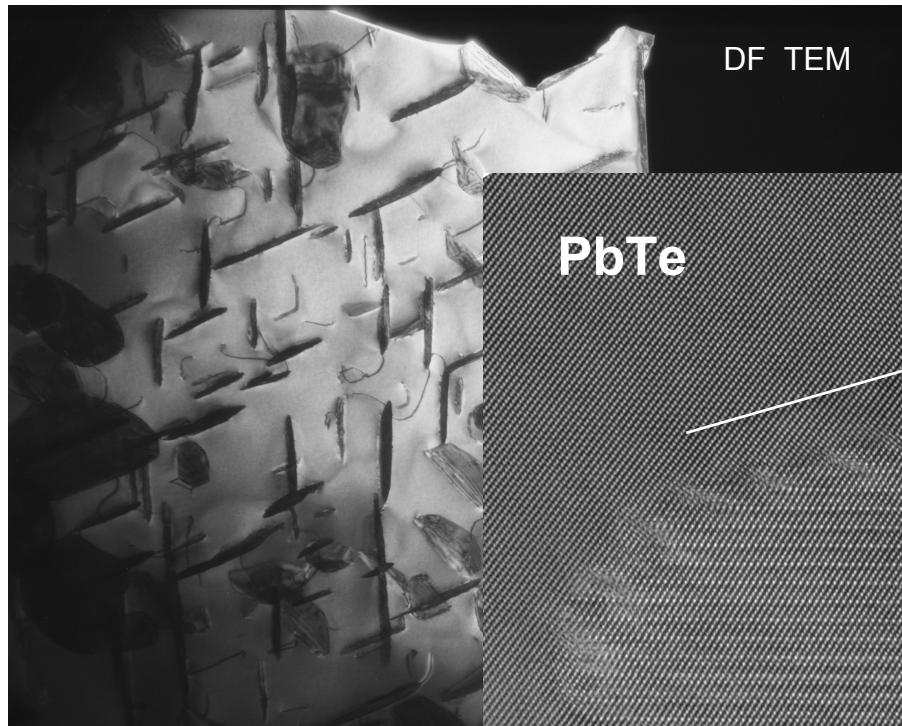
$$\mathbf{b}_{\parallel} = \frac{a_{cub}}{6}[\bar{1}2\bar{1}]$$

- Analogous to Shockley partial Dislocation
- $|\mathbf{b}_{\parallel}| = 2.48 \text{ \AA}$

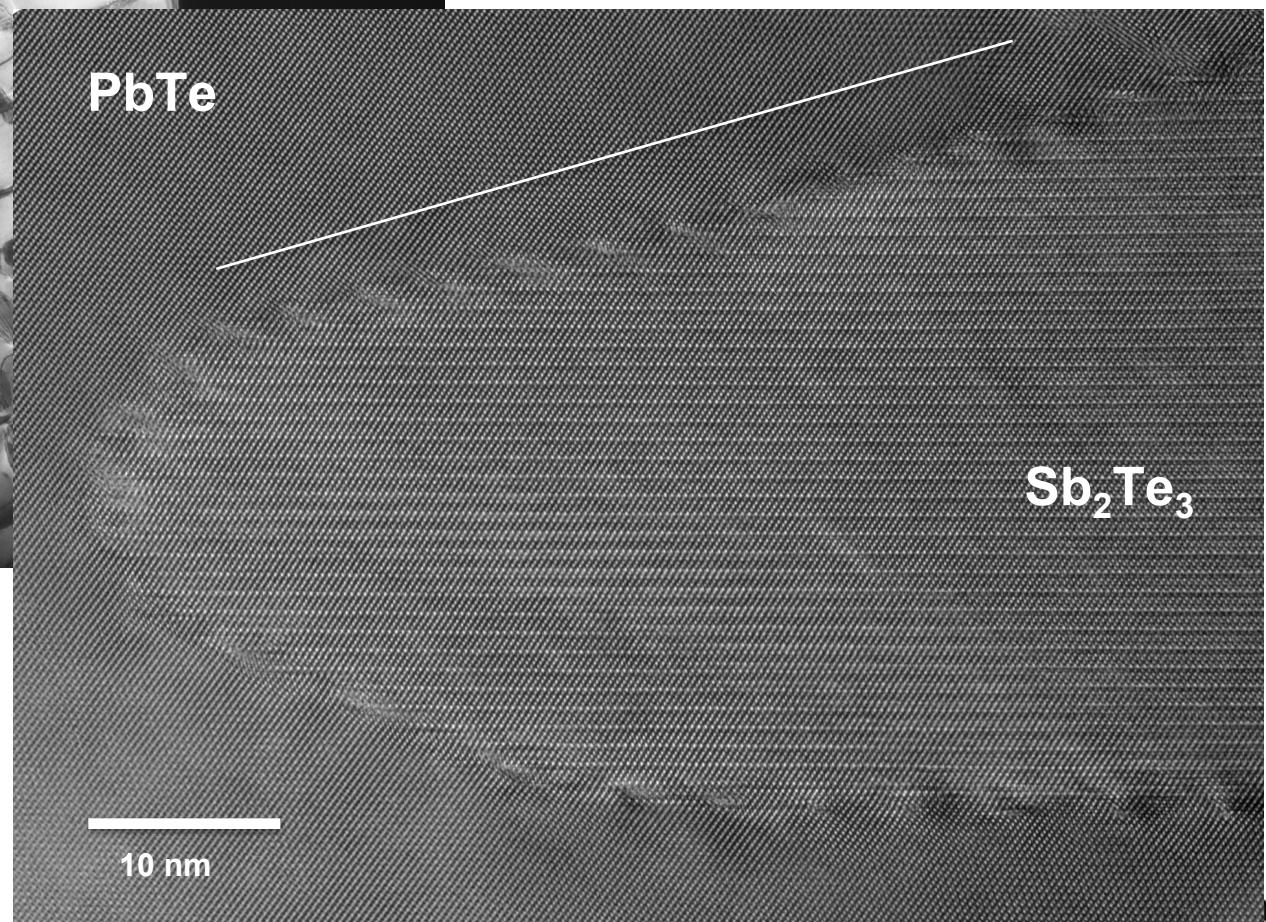


# A system with larger misfit: $\text{PbTe}/\text{Sb}_2\text{Te}_3$

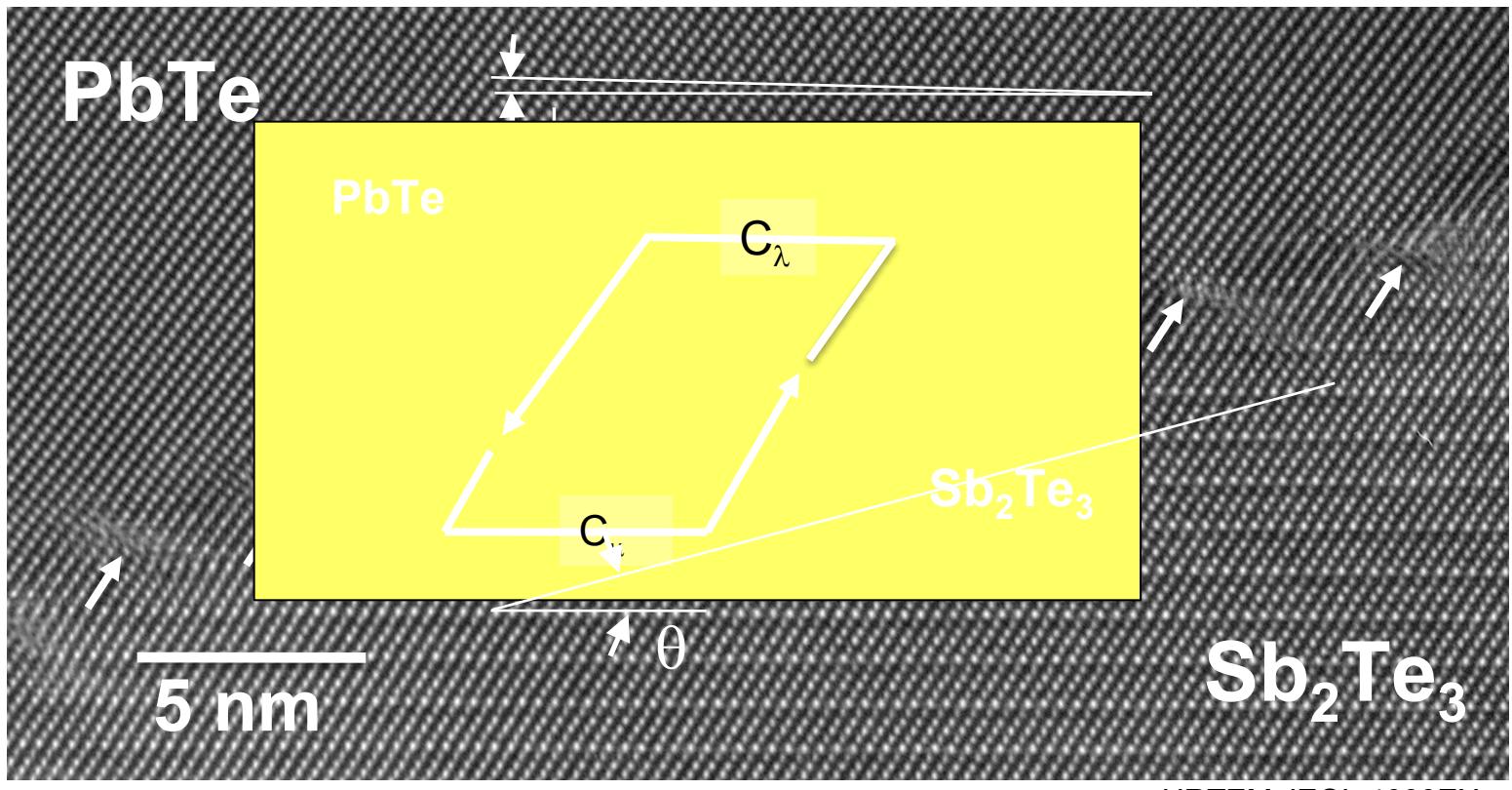
$\text{Sb}_2\text{Te}_3$  Precipitates in  $\text{PbTe}$



$\text{AgSbTe}_2(111)/\text{Sb}_2\text{Te}_3(0001)$   
Misfit: +0.79%



# Inclined Section of interface Composed of Disconnections



## Circuit Analysis:

Defects identical to the “6/5” disconnections observed in  $\text{AgSbTe}_2/\text{Sb}_2\text{Te}_3$

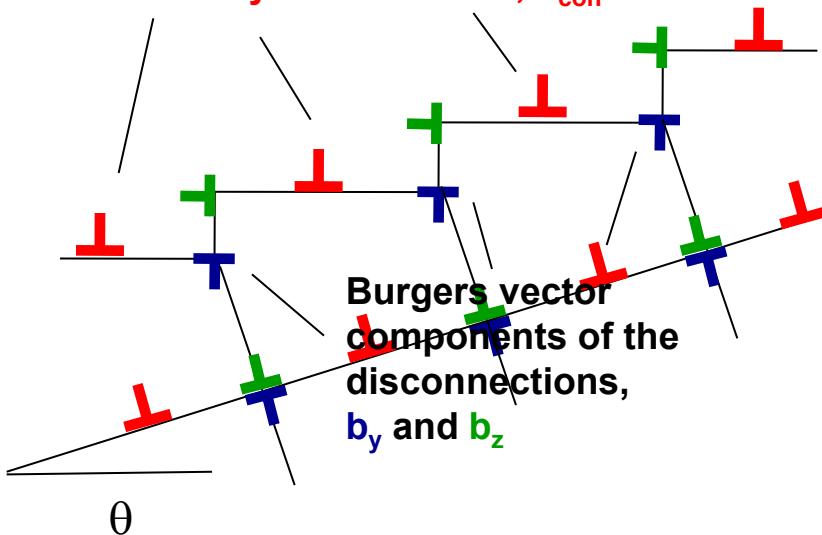
## Interface Geometry:

Inclination:  $\theta = 14.8^\circ$  Lattice rotation:  $\phi = 1.1^\circ$  to  $1.4^\circ$

# Interplay between Misfit Accommodation and Interface Inclination

Project components on inclined interface plane

Adjust spacing to cancel ( $\varepsilon_{yy} = 0$ )  
as "coherency" dislocations,  $b_{coh}$



$$-\varepsilon = (b_y \tan \theta + b_z \tan^2 \theta) h^{-1}$$

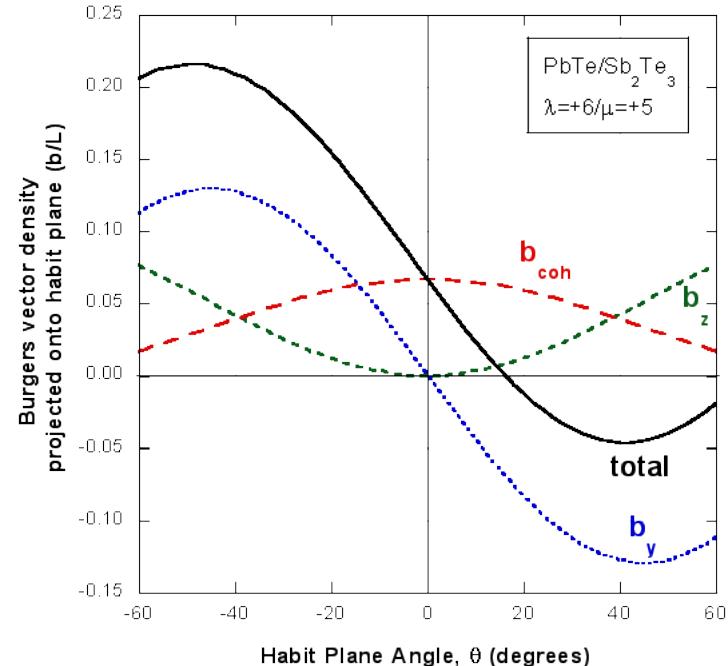
$$\rightarrow \theta = 16.2^\circ$$

Pond, Celotto, Hirth, Acta Mater. 2003

Out of plane **b** components produce small rigid body crystal rotation,

$$\phi = 2 \sin^{-1} [(b_z \cos \theta - b_y \sin \theta - \varepsilon h \cos \theta) \sin \theta / 2h] \rightarrow \phi = 1.7^\circ$$

**Disconnection spacing accommodates the (111)/(0001) coherency strain.**



# Conclusions

**Key structural aspects of the tetradymite-type chalcogenides are manifested in the detailed structures of extended defects in these materials.**

**Weak, van der Waals bonding across double chalcogenide layers**

**Ability to accommodate non-stoichiometry through altering the layer stacking**

**Close inter-relationship between the rocksalt and tetradymite structural types.**

**Attention to the topological properties and detailed structure of extended defects in the chalcogenides is critical.**

**Understanding interfacial formation and stability and, ultimately, interfacial transport properties in nanostructured bulk thermoelectrics.**

**Set of elementary "building blocks" for a general picture of interfacial structure in chalcogenide thermoelectrics**

# Acknowledgements

## Sandia/Livermore

**N.Y.C. Yang, C.Spataru, K. Erickson, J.D. Sugar**

## Sandia/Albuquerque

**M. Siegal, S. Limmer, W.G. Yelton**

## LBNL/NCEM

**Q. Ramasse (present address, SuperSTEM Laboratory, Daresbury, UK)**

## California Institute of Technology

**N.A. Heinz, T. Ikeda, G.J. Snyder**

### ***Special thanks to:***

**-LLNL: John Bradley, for use for LLNL's Titan 80/300 instrument**

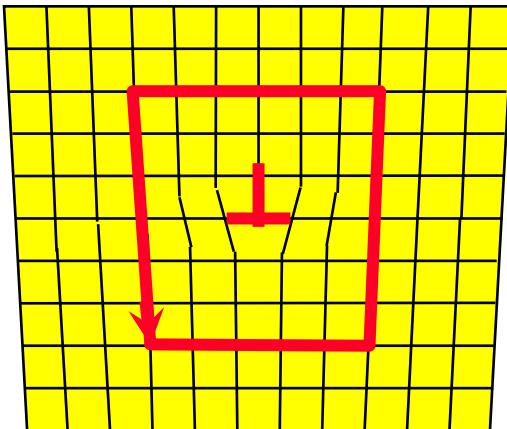
**-LBNL: User program, National Center for Electron Microscopy**

**-UCD: Z. Zhang and E. Lavernia, for assistance with bulk Bi<sub>2</sub>Te<sub>3</sub> processing**

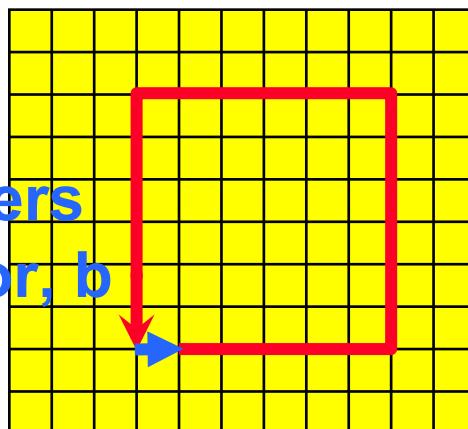
*Sandia National Laboratories is a multi-program laboratory managed and operated by Sandia Corporation, a wholly owned subsidiary of Lockheed Martin Corporation, for the U.S. Department of Energy's National Nuclear Security Administration under contract DE-AC04-94AL85000.*

# How do these structural considerations impact Dislocations and Interfaces?

Edge Dislocation

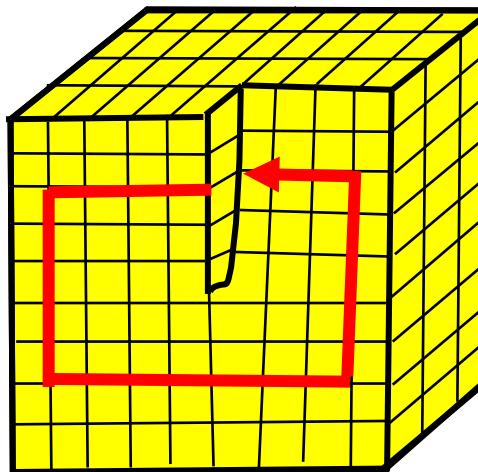


Reference Frame:  
**Perfect Crystal**

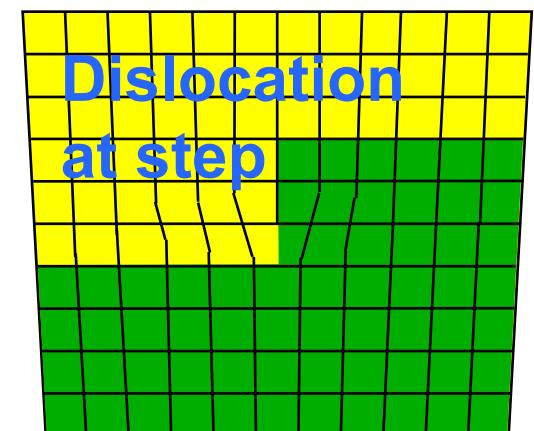
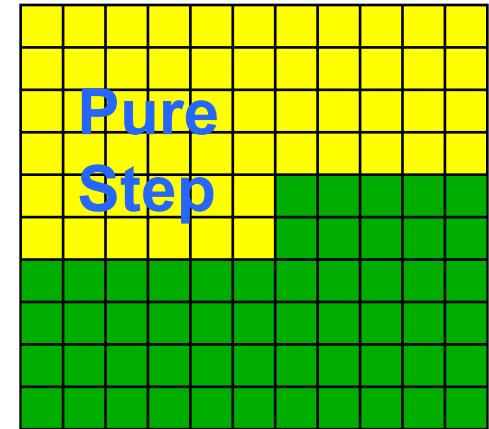


**Burgers  
Vector,  $\mathbf{b}$**

Screw Dislocation

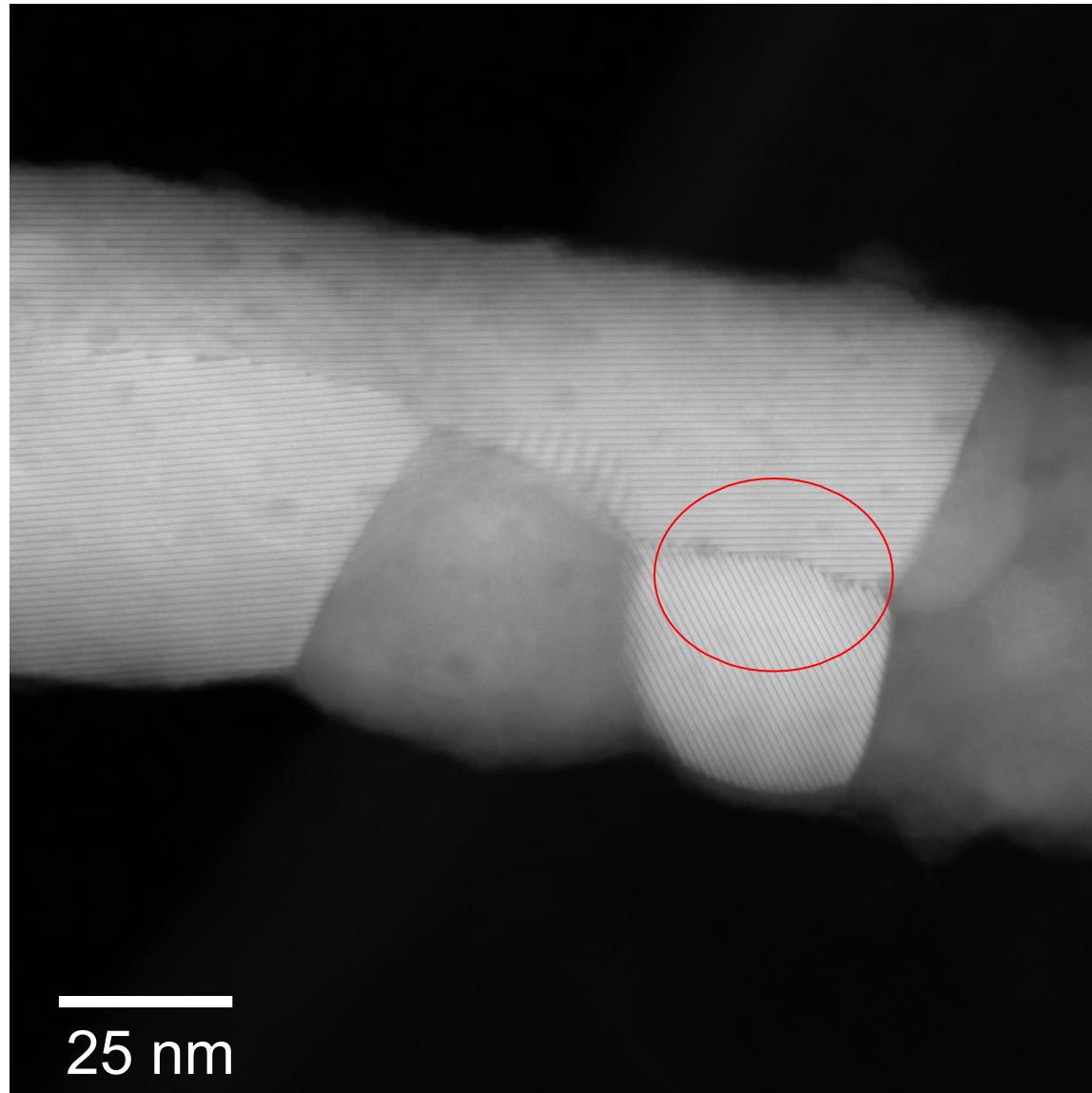


Interfacial Disconnection



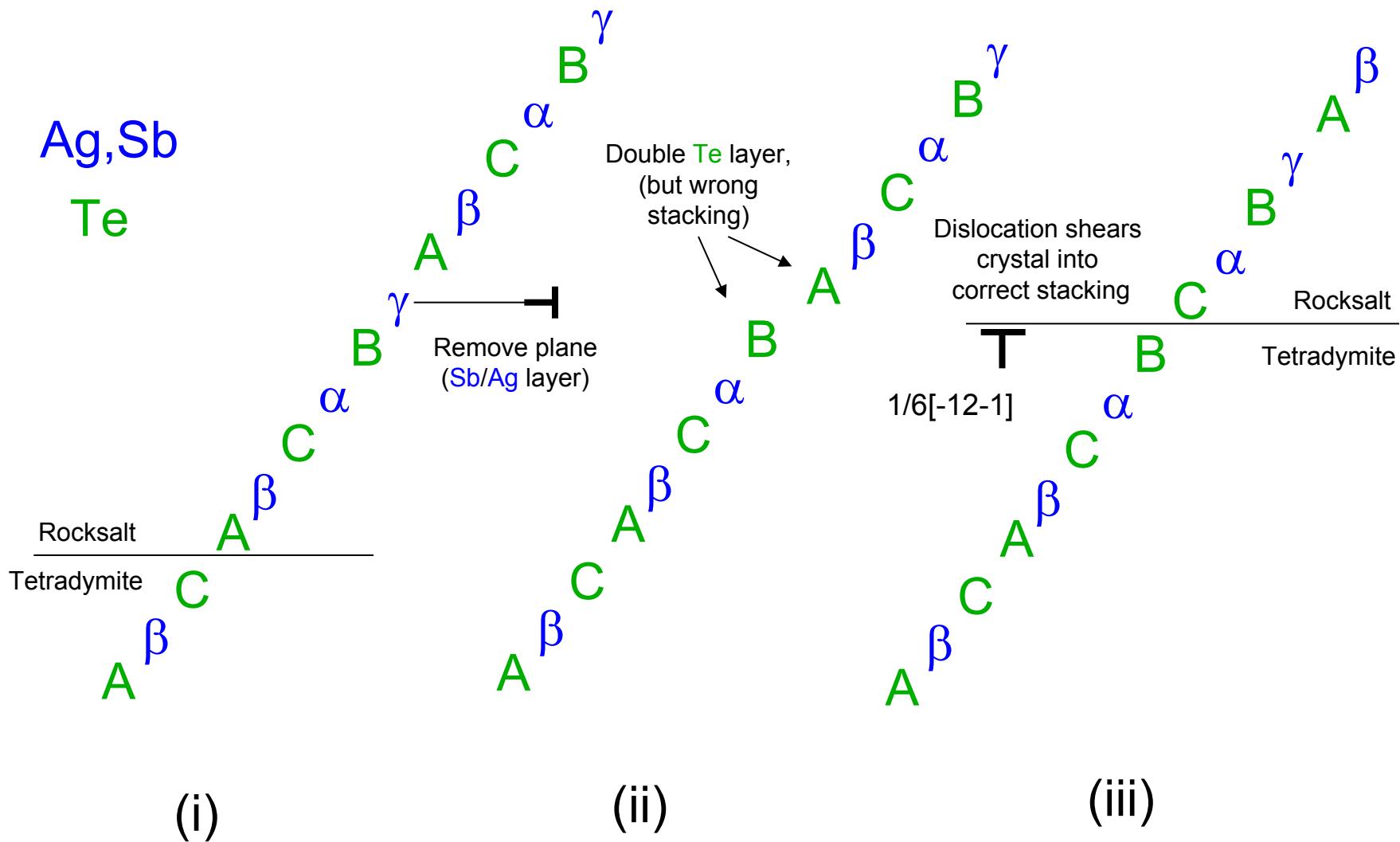
# Bi<sub>2</sub>Te<sub>3</sub> <2-1-1 0>/<-2 1 1 0> 63.78° Boundary

Electrodeposited  
Bi<sub>2</sub>Te<sub>3</sub> nanowire  
Annealed 300°C



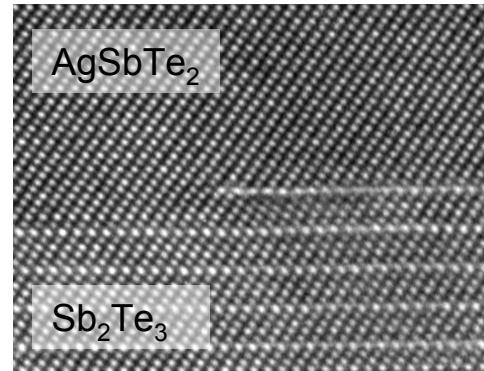
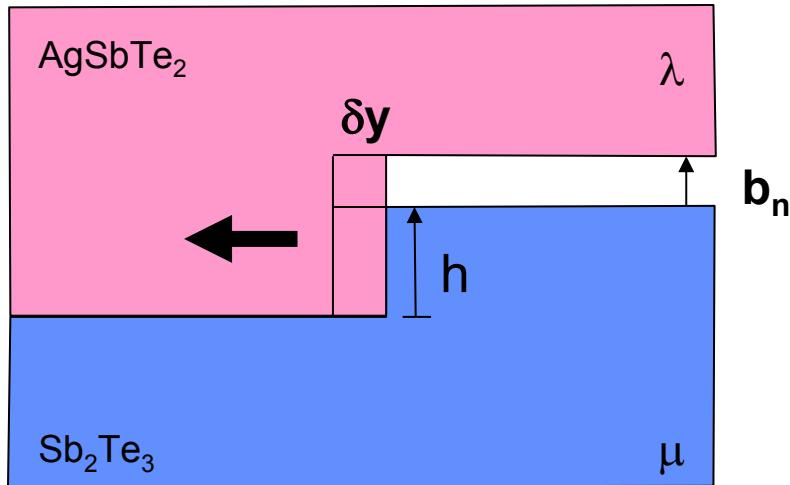
FEI-Titan  
HAADF-STEM  
300 keV

# Schematic of Transformation Sequence



# Defect properties give local mass flux required for transformation

Partition flux for defect motion into step and dislocation components



$$\frac{\Delta N_i}{L\delta y} = (\underbrace{\chi_i^\lambda - \chi_i^\mu}_{\text{step}})h + \underbrace{\chi_i^\lambda}_{\text{dislocation}} b_n$$

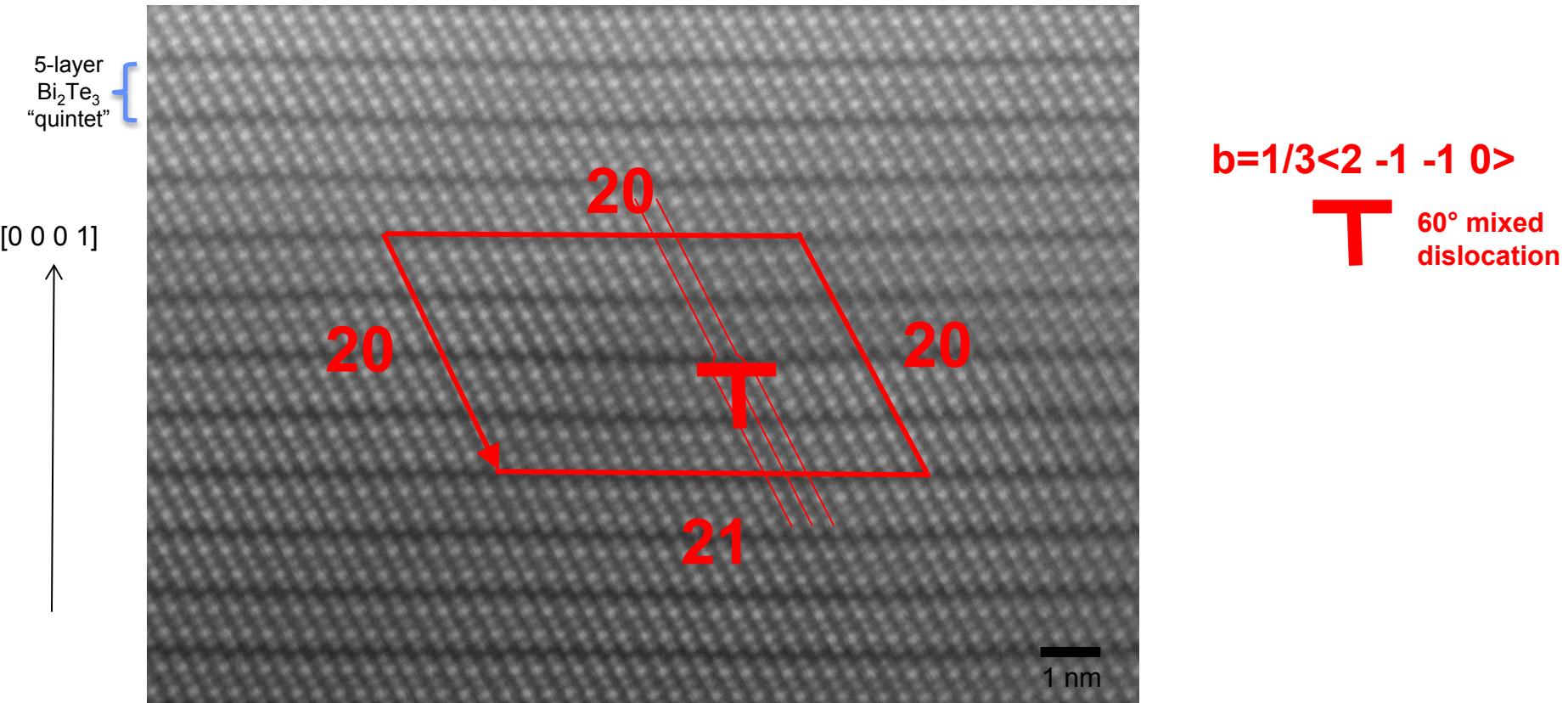
Hirth & Pond, Acta Mat 1996

Species	Step flux (atoms/Å <sup>2</sup> )	Dislocation flux (atom/Å <sup>2</sup> )	Total flux (atom/Å <sup>2</sup> )
Ag	$\frac{2 c_{hex}}{3 a_{cub}^3}$ +0.09043	$\frac{2}{a_{cub}^3} (\sqrt{3}a_{cub} - c_{hex}/3)$ +0.00334	$\frac{2\sqrt{3}}{a_{cub}^2}$ +0.09377
Sb	$\frac{2 c_{hex}}{3 a_{cub}^3} - \frac{8\sqrt{3}}{3a_{cub}^2}$ -0.03459	$\frac{2}{a_{cub}^3} (\sqrt{3}a_{cub} - c_{hex}/3)$ +0.00334	$-\frac{2\sqrt{3}}{3a_{cub}^2}$ -0.03126
Te	$-\frac{4}{a_{cub}^3} (\sqrt{3}a_{cub} - c_{hex}/3)$ -0.00668	$+\frac{4}{a_{cub}^3} (\sqrt{3}a_{cub} - c_{hex}/3)$ +0.00668	0

Reject Ag and Incorporate Sb in ratio of 3:1

Tellurium:  
Step and Dislocation fluxes cancel.  
No long-range Te transport required.

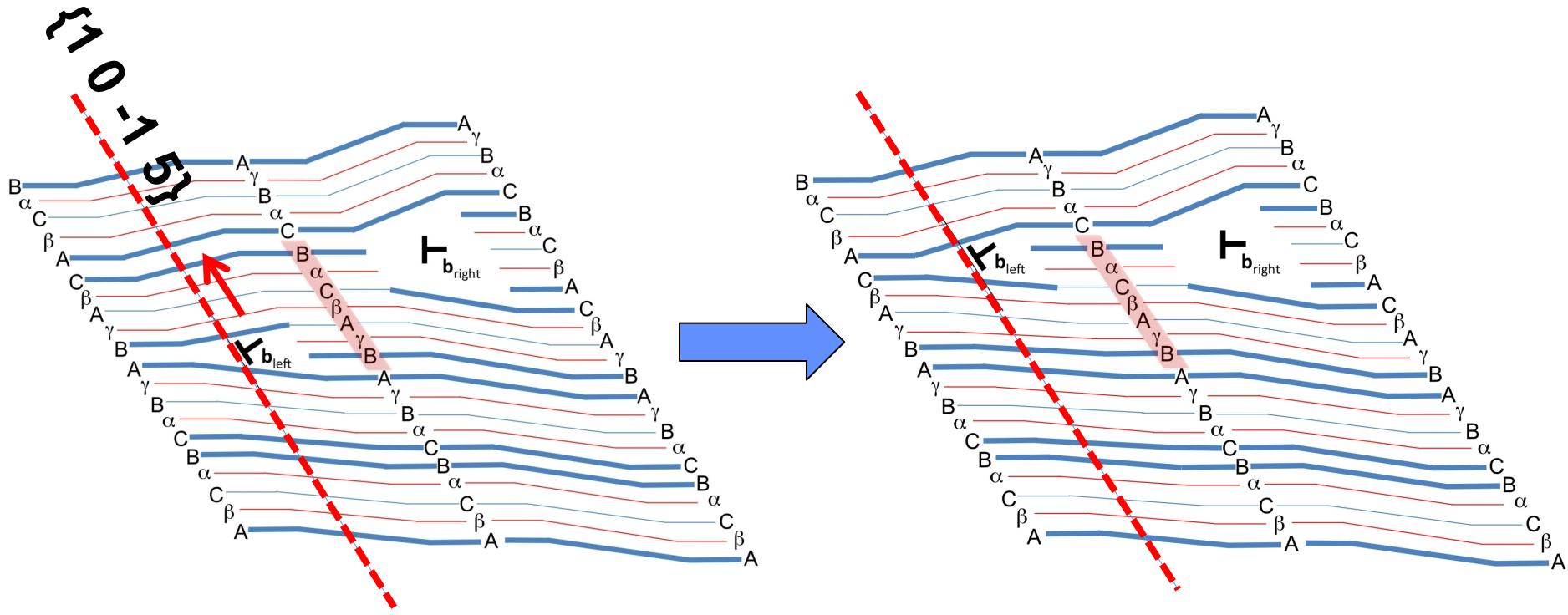
# Dislocation Core structure: termination at Te<sup>(1)</sup>-Te<sup>(1)</sup> layer, dissociation



FEI-Titan  
HAADF-STEM  
300 keV

<2 -1 -1 0 > projection

# Core can re-configure via glide of the left partial dislocation on $\{1\ 0\ -1\ 5\}$ plane



- $\{1\ 0\ -1\ 5\}$  is most densely packed plane in tetradymite structure  
-Analogous to  $\{001\}$  plane in rock-salt structure.